

1995 Index

IEEE Journal of Selected Topics in Quantum Electronics

Vol. 1

This index covers all technical items - papers, correspondence, reviews, etc. - that appeared in this periodical during 1995, and items from previous years that were commented upon or corrected in 1995.

The Author Index contains the primary entry for each item, listed under the first author's name, and cross-references from all coauthors. The Subject Index contains several entries for each item under appropriate subject headings, and subject cross-references.

It is always necessary to refer to the primary entry in the Author Index for the exact title, coauthors, and comments/corrections.

AUTHOR INDEX

A

- Abdulsabirov, R.Y.**, see Sarukura, N., *J-STQE Sep 95 792-804*
- Ackerman, D.A.**, G.E. Shtengel, M.S. Hybertsen, P.A. Morton, R.F. Kazarinov, T. Tanbun-Ek, and R.A. Logan. Analysis of gain in determining T_0 in 1.3 μm semiconductor lasers; *J-STQE Jun 95 250-263*
- Adachi, A.**, see Shima, A., *J-STQE Jun 95 102-109*
- Adams, A.R.**, see Meney, A.T., *J-STQE Jun 95 697-706*
- Ahmed, K.A.**, Kai Choong Chan, and Hai-Feng Liu. Femtosecond pulse generation from semiconductor lasers using the soliton-effect compression technique; *J-STQE Jun 95 592-600*
- Ahmed, Z.**, and R.S. Tucker. Small-signal IM response of grating-terminated external cavity semiconductor lasers; *J-STQE Jun 95 505-515*
- Ahn Doyeol**, see Doyeol Ahn, *J-STQE Jun 95 301-307*
- Albrektsen, O.**, see Salzman, J., *J-STQE Jun 95 346-355*
- Allerman, A.A.**, see Smith, P.B., *J-STQE Dec 95 1011-1016*
- Amann, M.-C.**, B. Borchert, S. Illek, and T. Wolf. Distributed forward coupled (DFC) laser; *J-STQE Jun 95 387-395*
- Andersen, D.R.**, see Hill, D.E., *J-STQE Jun 95 150-164*
- Aoki, M.**, see Okai, M., *J-STQE Jun 95 461-465*
- Arnold, J.M.**, see Khalifin, V.B., *J-STQE Jun 95 523-527*
- Arnold, W.H.**, P. Hagelstein, M. Obara, and R. Waynant. Introduction to the issue on short wavelength lasers and applications; *J-STQE Sep 95 765-767*
- Arora, B.M.**, see Ghosh, S., *J-STQE Dec 95 1108-1112*
- Aspnes, D.E.** Optical approaches to the determination of composition of semiconductor alloys during epitaxy; *J-STQE Dec 95 1054-1063*
- Astfalk, G.**, see Carver, G.E., *J-STQE Dec 95 980-986*
- Avrutin, E.A.**, see Portnoi, E.L., *J-STQE Jun 95 451-460*
- Avrutin, E.A.**, see Martins-Filho, J.F., *J-STQE Jun 95 539-551*
- Awschalom, D.D.**, see Crooker, S.A., *J-STQE Dec 95 1082-1092*
- Azouz, A.**, N. Stelmakh, P. Langlois, J.-M. Lourtioz, and P. Gavrilovic. Nonlinear chirp compensation in high-power broad-spectrum pulses from single-stripe mode-locked laser diodes; *J-STQE Jun 95 577-582*

B

- Baba, T.**, see Yuri, M., *J-STQE Jun 95 473-479*
- Bacher, K.**, see Eng, L.E., *J-STQE Jun 95 624-628*
- Bajaj, K.K.**, see Feng, Z.C., *J-STQE Dec 95 1119-1125*
- Balakireva, L.L.**, and I.V. Kozhevnikov. Computer simulation of damage to $\text{CrB}_2\text{-C}$ multilayer mirror in double-pass experiment with Ta laser; *J-STQE Sep 95 962-969*
- Barber, D.B.**, see Pollock, C.R., *J-STQE Apr 95 62-66*
- Barber, P.R.**, see Pask, H.M., *J-STQE Apr 95 2-13*
- Barber, R.**, see Fallahi, M., *J-STQE Jun 95 382-386*
- Barrow, D.A.**, see Portnoi, E.L., *J-STQE Jun 95 451-460*
- Basiev, T.**, see Mirov, S.B., *J-STQE Apr 95 22-30*
- Benyon, B.**, see Hanh Lu, *J-STQE Jun 95 375-381*
- Bethea, C.G.**, see Passlack, M., *J-STQE Jun 95 110-116*
- Bethea, C.G.**, see Fang, W.-C.W., *J-STQE Jun 95 117-128*
- Bewtra, N.**, D.A. Suda, G.L. Tan, F. Chatenoud, and J.M. Xu. Modeling of quantum-well lasers with electro-opto-thermal interaction; *J-STQE Jun 95 331-340*
- Bhattacharya, A.**, see Zmudzinski, C., *J-STQE Jun 95 129-137*
- Biernacki, P.D.**, H. Lee, and A.R. Mickelson. Evaluation of defect related diffusion in semiconductors by electrooptical sampling; *J-STQE Dec 95 1037-1046*

- Bimberg, D.**, see Schell, M., *J-STQE Jun 95 528-534*
- Blaauw, C.**, see Hanh Lu, *J-STQE Jun 95 375-381*
- Blood, P.**, and P. Smowton. Strain dependence of threshold current in fixed-wavelength GaInP laser diodes; *J-STQE Jun 95 707-711*
- Bode, G.H.**, see Tobin, R.C., *J-STQE Sep 95 805-810*
- Borchert, B.**, see Amann, M.-C., *J-STQE Jun 95 387-395*
- Botcharev, A.**, see Grann, E.D., *J-STQE Dec 95 1093-1099*
- Botez, D.**, and R.S. Tucker. Introduction to the special issue on semiconductor lasers; *J-STQE Jun 95 100-101*
- Botez, D.**, see Zmudzinski, C., *J-STQE Jun 95 129-137*
- Botez, D.**, see Nabiev, R.F., *J-STQE Jun 95 138-149*
- Bowers, J.E.**, see Uskov, A.V., *J-STQE Jun 95 552-561*
- Brown, D.J.W.**, see Coutts, D.W., *J-STQE Sep 95 768-778*
- Brown, D.J.W.**, see Withford, M.J., *J-STQE Sep 95 779-783*
- Burkhard, H.**, see Hainsmann, S., *J-STQE Jun 95 341-345*
- Burkhard, H.**, see Hillmer, H., *J-STQE Jun 95 356-362*
- Burrows, E.C.**, see Kang-Yih Liou, *J-STQE Jun 95 165-172*
- Burrus, C.A.**, see Kang-Yih Liou, *J-STQE Jun 95 165-172*

C

- Cairns, G.F.**, see Healy, S.B., *J-STQE Sep 95 949-957*
- Cairns, G.F.**, see Healy, S.B., *J-STQE Dec 95 1156*
- Caneau, C.**, see Wu, Y.A., *J-STQE Jun 95 629-637*
- Carman, R.J.**, see Pask, H.M., *J-STQE Apr 95 2-13*
- Carroll, J.E.**, see Nowell, M.C., *J-STQE Jun 95 433-441*
- Carver, G.E.**, R.W. Heebner, and G. Astfalk. Wafer level testing for semiconductor laser manufacture via spatially resolved photoluminescence; *J-STQE Dec 95 980-986*
- Castex, M.C.**, see Muscur, L., *J-STQE Sep 95 900-907*
- Celii, F.G.**, T.S. Moise, Y.-C. Kao, and A.J. Katz. Optical diagnostic monitoring of resonant-tunneling diode growth; *J-STQE Dec 95 1064-1072*
- Cen, J.**, see Feng, Z.C., *J-STQE Dec 95 1119-1125*
- Chai, B.H.T.**, see Marshall, C.D., *J-STQE Apr 95 67-77*
- Chakrabarti, U.K.**, see Passlack, M., *J-STQE Jun 95 110-116*
- Chang, C.-S.**, S.L. Chuang, J.R. Minch, W.W. Fang, Y.K. Chen, and T. Tanbun-Ek. Amplified spontaneous emission spectroscopy in strained quantum-well lasers; *J-STQE Dec 95 1100-1107*
- Chang Chih-Sheng**, see Chih-Sheng Chang, *J-STQE Jun 95 218-229*
- Chang-Hasnain, C.J.**, see Nabiev, R.F., *J-STQE Jun 95 234-243*
- Chang-Hasnain, C.J.**, see Eng, L.E., *J-STQE Jun 95 624-628*
- Chang-Hasnain, C.J.**, see Wu, Y.A., *J-STQE Jun 95 629-637*
- Chang Ji-Ho**, see Won-Jin Choi, *J-STQE Jun 95 717-722*
- Chan Kai Choong**, see Ahmed, K.A., *J-STQE Jun 95 592-600*
- Chatenoud, F.**, see Dion, M., *J-STQE Jun 95 230-233*
- Chatenoud, F.**, see Bewtra, N., *J-STQE Jun 95 331-340*
- Chatenoud, F.**, see Fallahi, M., *J-STQE Jun 95 382-386*
- Chen, Y.K.**, see Fang, W.-C.W., *J-STQE Jun 95 117-128*
- Chen, Y.K.**, see Chang, C.-S., *J-STQE Dec 95 1100-1107*
- Cheng Yong**, see Hanmin Zhao, *J-STQE Jun 95 196-202*
- Chih-Sheng Chang**, and Shun Lien Chuang. Modeling of strained quantum-well lasers with spin-orbit coupling; *J-STQE Jun 95 218-229*
- Chik, G.**, see Evans, J.D., *J-STQE Jun 95 275-284*
- Chilla, J.L.A.**, see Rocca, J.J., *J-STQE Sep 95 945-948*
- Chin-Yao Tsai**, see Chin-Yi Tsai, *J-STQE Jun 95 316-330*
- Chin-Yi Tsai**, Chin-Yao Tsai, Yu-Hwa Lo, R.M. Spencer, and L.F. Eastman. Nonlinear gain coefficients in semiconductor quantum-well lasers: effects of carrier diffusion, capture, and escape; *J-STQE Jun 95 316-330*
- Chi Zhou, Qi Wang, Zuguang Ma, and Sining Li.** VUV spectra of rare-gas fluoride ionic excimers; *J-STQE Sep 95 872-876*
- Choi Won-Jin**, see Won-Jin Choi, *J-STQE Jun 95 717-722*
- Choi Won-Taek**, see Won-Jin Choi, *J-STQE Jun 95 717-722*
- Choong Chan Kai**, see Ahmed, K.A., *J-STQE Jun 95 592-600*
- Choquette, K.D.**, see Zhang, T., *J-STQE Jun 95 606-615*
- Choquette, K.D.**, see Wu, Y.A., *J-STQE Jun 95 629-637*
- Choquette, K.D.**, R.P. Schneider, K.L. Lear, and R.E. Leibenguth. Gain-dependent polarization properties of vertical-cavity lasers; *J-STQE Jun 95 661-666*
- Chow, D.H.**, see Yong-Hang Zhang, *J-STQE Jun 95 749-756*
- Chow, W.W.**, M.H. Crawford, and R.P. Schneider, Jr. Minimization of threshold current in short wavelength AlGaInP vertical-cavity surface-emitting lasers; *J-STQE Jun 95 649-653*
- Chuang, S.L.**, see Chang, C.-S., *J-STQE Dec 95 1100-1107*

- Chuang Shun Lien, *see* Fang, W.-C.W., *J-STQE Jun 95* 117-128
 Chuang Shun Lien, *see* Chih-Sheng Chang, *J-STQE Jun 95* 218-229
 Clark, D.P., *see* Rocca, J.J., *J-STQE Sep 95* 945-948
 Coldren, L.A., *see* Scott, J.W., *J-STQE Jun 95* 638-648
 Cooper, D.G., J.L. Dexter, and R.D. Esman. Widely tunable polarization-stable fiber lasers; *J-STQE Apr 95* 14-21
 Coutts, D.W., and D.J.W. Brown. Production of high average power UV by second-harmonic and sum-frequency generation from copper-vapor lasers; *J-STQE Sep 95* 768-778
 Crawford, M.H., *see* Chow, W.W., *J-STQE Jun 95* 649-653
 Crooker, S.A., D.D. Awschalom, and N. Samarth. Time-resolved Faraday rotation spectroscopy of spin dynamics in digital magnetic heterostructures; *J-STQE Dec 95* 1082-1092

D

- Dadap, J.I., X.F. Hu, N.M. Russell, J.G. Ekerdt, J.K. Lowell, and M.C. Downer. Analysis of second-harmonic generation by amplified, high-repetition-rate, ultrashort laser pulses at Si(001) interfaces; *J-STQE Dec 95* 1145-1155
 Dapkus, P.D., *see* Hanmin Zhao, *J-STQE Jun 95* 196-202
 Dasgupta, S., *see* Hill, D.E., *J-STQE Jun 95* 150-164
 Dawes, J.M., *see* Pask, H.M., *J-STQE Apr 95* 2-13
 de Jong, J.F., *see* Passlack, M., *J-STQE Jun 95* 110-116
 Delansay, P., *see* Jong-In Shim, *J-STQE Jun 95* 408-415
 Delaporte, P., *see* Tischler, H., *J-STQE Sep 95* 877-885
 Delaporte, P., *see* Tischler, H., *J-STQE Sep 95* 886-890
 DeLaRue, R.M., *see* Krauss, T.F., *J-STQE Jun 95* 757-761
 Delorme, F., S. Slempek, A. Ramdane, B. Rose, and K. Nakajima. Subnanosecond tunable distributed Bragg reflector lasers with an electrooptical Bragg section; *J-STQE Jun 95* 396-400
 Dennis, T., H.M. Duiker, Jun Wu, C. Toth, and J.F. Young. Comparison of laser-produced plasma target materials for pumping the 109-nm Xe²⁺ Auger laser; *J-STQE Sep 95* 867-871
 Dexter, J.L., *see* Cooper, D.G., *J-STQE Apr 95* 14-21
 Dick, S., *see* Dion, M., *J-STQE Jun 95* 230-233
 Dion, M., Z.-M. Li, D. Ross, F. Chatenoud, R.L. Williams, and S. Dick. A study of the temperature sensitivity of GaAs-(Al,Ga)As multiple quantum-well GRINSCHE lasers; *J-STQE Jun 95* 230-233
 Dion, M., *see* Fallahi, M., *J-STQE Jun 95* 382-386
 Donko, Z., *see* Tobin, R.C., *J-STQE Sep 95* 805-810
 Downer, M.C., *see* Dadap, J.I., *J-STQE Dec 95* 1145-1155
 Doyeol Ahn. The theory of non-Markovian gain in semiconductor lasers; *J-STQE Jun 95* 301-307
 Dubinskii, M.A., *see* Sarukura, N., *J-STQE Sep 95* 792-804
 Duiker, H.M., *see* Dennis, T., *J-STQE Sep 95* 867-871
 Duncan, W.M., *see* Smith, P.B., *J-STQE Dec 95* 1011-1016
 Dunstan, D.J., *see* Meney, A.T., *J-STQE Jun 95* 697-706
 Dutta, N.K., *see* Passlack, M., *J-STQE Jun 95* 110-116
 Duttagupta, S.P., *see* Fauchet, P.M., *J-STQE Dec 95* 1126-1139

E

- Eastman, L.F., *see* Chin-Yi Tsai, *J-STQE Jun 95* 316-330
 Ebeling, K.J., *see* Fiedler, U., *J-STQE Jun 95* 442-450
 Ebeling, K.J., *see* Zeeb, E., *J-STQE Jun 95* 616-623
 Edamatsu, K., *see* Sarukura, N., *J-STQE Sep 95* 792-804
 Eden, J.G., *see* Funk, D.S., *J-STQE Sep 95* 784-791
 Eguchi, N., *see* Oka, M., *J-STQE Sep 95* 859-866
 Eisenstein, G., *see* Tessler, N., *J-STQE Jun 95* 490-493
 Ekerdt, J.G., *see* Dadap, J.I., *J-STQE Dec 95* 1145-1155
 Eng, L.E., K. Bacher, Wupen Yuen, J.S. Harris, Jr., and C.J. Chang-Hasnain. Multiple-wavelength vertical cavity laser arrays on patterned substrates; *J-STQE Jun 95* 624-628
 Esman, R.D., *see* Cooper, D.G., *J-STQE Apr 95* 14-21
 Esterowitz, L. Introduction to the issue on tunable solid-state lasers; *J-STQE Apr 95* 1
 Esterowitz, L., *see* Pinto, J.F., *J-STQE Apr 95* 58-61
 Esterowitz, L., *see* Stoneman, R.C., *J-STQE Apr 95* 78-81
 Evans, J.D., J.G. Simmons, D.A. Thompson, N. Puetz, T. Makino, and G. Chik. An investigation into the temperature sensitivity of strained and unstrained multiple quantum-well, long wavelength lasers: new insight and methods of characterization; *J-STQE Jun 95* 275-284
 Ezaki, M., H. Kumagai, K. Toyoda, and M. Obara. Surface modification of III-V compound semiconductors using surface electromagnetic wave etching induced by ultraviolet lasers; *J-STQE Sep 95* 841-847

F

- Fallahi, M., F. Chatenoud, M. Dion, I. Templeton, R. Barber, and J. Thompson. Circular-grating surface-emitting distributed Bragg reflector lasers on an InGaAs-GaAs structure for 0.48- μ m applications; *J-STQE Jun 95* 382-386
 Fang, W.-C.W., C.G. Bethea, Y.K. Chen, and Shun Lien Chuang. Longitudinal spatial inhomogeneities in high-power semiconductor lasers; *J-STQE Jun 95* 117-128
 Fang, W.W., *see* Chang, C.-S., *J-STQE Dec 95* 1100-1107
 Fauchet, P.M., L. Tsybeskov, C. Peng, S.P. Duttagupta, J. von Behren, Y. Kostoulas, J.M.V. Vandyshev, and K.D. Hirschman. Light-emitting porous silicon: Materials science, properties, and device applications; *J-STQE Dec 95* 1126-1139
 Feiste, U., *see* Sartorius, B., *J-STQE Jun 95* 535-538
 Feng, Z.C., S. Perkowitz, J. Cen, K.K. Bajaj, D.K. Kinell, and R.L. Whitney. Photoluminescence, Raman, and infrared diagnosis of GaAs-AlGaAs superlattices for intersubband infrared detection; *J-STQE Dec 95* 1119-1125
 Ferry, D.K., *see* Grann, E.D., *J-STQE Dec 95* 1093-1099
 Fiedler, U., and K.J. Ebeling. Design of VCSEL's for feedback insensitive data transmission and external cavity active mode-locking; *J-STQE Jun 95* 442-450
 Fill, E.E., Yuelin Li, and G. Pretzler. Study of neon-like lasing in gallium; *J-STQE Sep 95* 958-961
 Filoche, M., *see* Kazmierski, C., *J-STQE Jun 95* 371-374
 Fontaine, B., *see* Tischler, H., *J-STQE Sep 95* 877-885
 Forte, A.R., *see* Rothschild, M., *J-STQE Sep 95* 916-923
 Fouquet, J.E., and J.L. Merz. Optical diagnostics of semiconductors [special issue intro.]; *J-STQE Dec 95* 977-979
 Fujii, T., *see* Inoue, S., *J-STQE Sep 95* 908-915
 Fujikawa, S., *see* Sato, Y., *J-STQE Sep 95* 811-824
 Fukumoto, J.M., *see* Komine, H., *J-STQE Apr 95* 44-49
 Fukushima, I., *see* Irikawa, M., *J-STQE Jun 95* 285-292
 Funabashi, M., *see* Sudoh, T.K., *J-STQE Jun 95* 583-591
 Funemizu, M., *see* Tohyama, M., *J-STQE Jun 95* 416-426
 Funk, D.S., and J.G. Eden. Glass-fiber lasers in the ultraviolet and visible; *J-STQE Sep 95* 784-791

G

- Gavrilovic, P., *see* Azouz, A., *J-STQE Jun 95* 577-582
 Ghaemi, H.F., *see* Goldberg, B.B., *J-STQE Dec 95* 1073-1081
 Ghosh, S., and B.M. Arora. Double AC photoreflectance spectroscopy of semiconductors; *J-STQE Dec 95* 1108-1112
 Glover, A.C.J., E.K. Ily, and J.A. Piper. High-speed UV micro-machining of polymers with frequency-doubled copper vapor lasers; *J-STQE Sep 95* 830-836
 Goldberg, B.B., M.S. Unlu, W.D. Herzog, H.F. Ghaemi, and E. Towe. Near-field optical studies of semiconductor heterostructures and laser diodes; *J-STQE Dec 95* 1073-1081
 Goldberg, L., *see* Hall, D.C., *J-STQE Dec 95* 1017-1029
 Gorfinkel, V.B., *see* Portnoi, E.L., *J-STQE Jun 95* 451-460
 Grabmaier, A., *see* Hillmer, H., *J-STQE Jun 95* 356-362
 Grann, E.D., S. Sheih, K.T. Tsen, S. Guncer, D.K. Ferry, A. Salvador, A. Botcharev, and H. Morkoc. Nonequilibrium electron distributions and high-field electron transport in an Al_xGa_{1-x}As-based p-i-n nanostructure semiconductor - A picosecond Raman probe; *J-STQE Dec 95* 1093-1099
 Grantham, J.W., *see* Sun, D., *J-STQE Jun 95* 674-680
 Gray, M.L., *see* Pollak, F.H., *J-STQE Dec 95* 1002-1010
 Griffin, R.A., D.A. Jackson, and D.D. Sampson. Coherence and noise properties of gain-switched Fabry-Perot semiconductor lasers; *J-STQE Jun 95* 569-576
 Guncer, S., *see* Grann, E.D., *J-STQE Dec 95* 1093-1099
 Guodong Zhang. Influence of strain on lasing performances of Al-free strained-layer Ga(In)As(P)-GaInAsP-GaN quantum-well lasers emitting at 0.78- λ <1.1 μ m; *J-STQE Jun 95* 183-188
 Guo Ping Li, *see* Hanh Lu, *J-STQE Jun 95* 375-381
 Gurney, P.C.R., *see* Nguyen, L.V.T., *J-STQE Jun 95* 494-504
 Gye-Mo Yang, *see* Hanmin Zhao, *J-STQE Jun 95* 196-202

H

- Hackbarth, T., *see* Zeeb, E., *J-STQE Jun 95* 616-623
 Hagelstein, P., *see* Arnold, W.H., *J-STQE Sep 95* 765-767
 Hai-Feng Liu, *see* Ahmed, K.A., *J-STQE Jun 95* 592-600
 Hall, D.C., and L. Goldberg. Interferometric near-field imaging technique for phase and refractive index profiling in large-area planar-waveguide optoelectronic devices; *J-STQE Dec 95* 1017-1029
 Hanabusa, M., and K. Tsujihara. Deposition of diamond-like carbon films by excimer lasers using frozen acetylene; *J-STQE Sep 95* 848-851

- Hanberg, J., see Salzman, J., *J-STQE Jun 95 346-355*
 Hanh Lu, C. Blaauw, B. Benyon, Guo Ping Li, and T. Makino. High-power and high-speed performance of 1.3- μm strained MQW gain-coupled DFB lasers; *J-STQE Jun 95 375-381*
 Hanmin Zhao, M.H. MacDougall, P.D. Dapkus, K. Uppal, Yong Cheng, and Gye-Mo Yang. Submilliampere threshold current InGaAs-GaAs-AlGaAs lasers and laser arrays grown on nonplanar substrates; *J-STQE Jun 95 196-202*
 Hanna, D.C., see Pask, H.M., *J-STQE Apr 95 2-13*
 Hansmann, S., H. Hillmer, H. Walter, H. Burkhard, B. Hubner, and E. Kuphal. Variation of coupling coefficients by sampled gratings in complex coupled distributed-feedback lasers; *J-STQE Jun 95 341-345*
 Hansmann, S., see Hillmer, H., *J-STQE Jun 95 356-362*
 Hara, K., see Kobayashi, R., *J-STQE Jun 95 723-727*
 Harned, N., J. McClay, and J.J. Shamaly. Laser-damage impact on lithography system throughput; *J-STQE Sep 95 837-840*
 Harris, J.S., Jr., see Eng, L.E., *J-STQE Jun 95 624-628*
 Harris, S., Jr., see Yuri, M., *J-STQE Jun 95 473-479*
 Haruta, K., see Sato, Y., *J-STQE Sep 95 811-824*
 Hatori, N., see Mukaijara, T., *J-STQE Jun 95 667-673*
 Hayashi, Y., see Mukaijara, T., *J-STQE Jun 95 667-673*
 Healy, S.B., G.F. Cairns, C.L.S. Lewis, G.J. Pert, and J.A. Plowes. A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses; *J-STQE Sep 95 949-957*
 Healy, S.B., G.F. Cairns, C.L.S. Lewis, G.J. Pert, and J.A. Plowes. Correction to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957); *J-STQE Dec 95 1156*
 Heebner, R.W., see Carver, G.E., *J-STQE Dec 95 980-986*
 Herman, I.P. Real-time optical thermometry during semiconductor processing; *J-STQE Dec 95 1047-1053*
 Herzog, W.D., see Goldberg, B.B., *J-STQE Dec 95 1073-1081*
 Hill, D.E., S. Dasgupta, K.M. Nagpal, and D.R. Andersen. Feedback stabilization of semiconductor laser arrays with complex coupling coefficients; *J-STQE Jun 95 150-164*
 Hillmer, H., see Hansmann, S., *J-STQE Jun 95 341-345*
 Hillmer, H., A. Grabmaier, S. Hansmann, H.-L. Zhu, H. Burkhard, and K. Magari. Tailored DFB laser properties by individually chirped gratings using bent waveguides; *J-STQE Jun 95 356-362*
 Hiramoto, K., see Sagawa, M., *J-STQE Jun 95 189-194*
 Hirata, T., see Sudoh, T.K., *J-STQE Jun 95 583-591*
 Hirayama, Y., see Irikawa, M., *J-STQE Jun 95 285-292*
 Hirschman, K.D., see Fauchet, P.M., *J-STQE Dec 95 1126-1139*
 Hobson, W.S., see Passlack, M., *J-STQE Jun 95 110-116*
 Hobson, W.S., see Pollak, F.H., *J-STQE Dec 95 1002-1010*
 Horn, M.W., see Rothschild, M., *J-STQE Sep 95 916-923*
 Hosoda, M., see Watanabe, M., *J-STQE Jun 95 728-733*
 Hotta, H., see Kobayashi, R., *J-STQE Jun 95 723-727*
 Hu, X.F., see Dadap, J.I., *J-STQE Dec 95 1145-1155*
 Hubner, B., see Hansmann, S., *J-STQE Jun 95 341-345*
 Huhse, D., see Schell, M., *J-STQE Jun 95 528-534*
 Hybertsen, M.S., see Ackerman, D.A., *J-STQE Jun 95 250-263*

I

- Iga, K., see Mukaijara, T., *J-STQE Jun 95 667-673*
 Igarashi, T., see Kawanaka, J., *J-STQE Sep 95 852-858*
 Illek, S., see Amann, M.-C., *J-STQE Jun 95 387-395*
 Illy, E.K., see Glover, A.C.J., *J-STQE Sep 95 830-836*
 Imafuji, O., see Yuri, M., *J-STQE Jun 95 473-479*
 Imafuji, O., see Takayama, T., *J-STQE Jun 95 562-568*
 Imler, W.R. High-speed photoluminescence mapping of III-V epitaxial layers for light emitting diodes; *J-STQE Dec 95 987-992*
 Inoue, M., see Sato, Y., *J-STQE Sep 95 811-824*
 Inoue, S., T. Fujii, Y. Ueno, and F. Kannari. F₂ laser deposition of CdTe microcrystallites-doped fluoropolymer thin films; *J-STQE Sep 95 908-915*
 Irikawa, M., H. Shimizu, I. Fukushima, K. Nishikata, and Y. Hirayama. Strained GaInAs-AlGaInAs 1.5- μm -wavelength multiquantum-well lasers loaded with GaInAs-AlInAs multiquantum barriers at the p-side optical confinement layer; *J-STQE Jun 95 285-292*
 Ironside, C.N., see Martins-Filho, J.F., *J-STQE Jun 95 539-551*
 Ishibashi, A. II-VI blue-green laser diodes; *J-STQE Jun 95 741-748*
 Ishii, H., F. Kano, Y. Tohmori, Y. Kondo, T. Tamamura, and Y. Yoshikuni. Narrow spectral linewidth under wavelength tuning in thermally tunable super-structure-grating (SSG) DBR lasers; *J-STQE Jun 95 401-407*
 Ishikawa, M., see Morinaga, M., *J-STQE Jun 95 427-432*
 Isyanova, Y., see Rines, G.A., *J-STQE Apr 95 50-57*
 Itoh, K., see Yuri, M., *J-STQE Jun 95 473-479*
 Itoh, K., see Takayama, T., *J-STQE Jun 95 562-568*

- Itoh, T., see Sarukura, N., *J-STQE Sep 95 792-804*
 Iwai, N., see Kasukawa, A., *J-STQE Jun 95 293-300*

J

- Jackson, D.A., see Griffin, R.A., *J-STQE Jun 95 569-576*
 Jaeger, A., G. Weiser, and P. Wiedemann. Inhomogeneous exciton broadening and mean free path in In_{1-x}Ga_xAs_yP_{1-y}InP heterostructures; *J-STQE Dec 95 1113-1118*
 Jansen Van Doorn, A.K., see van Exter, M.P., *J-STQE Jun 95 601-605*
 Ji-Ho Chang, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Jong-In Shim, M. Yamaguchi, P. Delansay, and M. Kitamura. Refractive index and loss changes produced by current injection in InGaAs(P)-InGaAsP multiple quantum-well (MQW) waveguides; *J-STQE Jun 95 408-415*
 Jong-In Shim, H. Olesen, H. Yamazaki, M. Yamaguchi, and M. Kitamura. 1.5- μm InGaAsP-InP multigain-levered-MQW-DFB-LD with high-efficiency and large-bandwidth FM response; *J-STQE Jun 95 516-522*
 Jong-Seok Kim, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Jonsson, B., see Salzman, J., *J-STQE Jun 95 346-355*
 Jopson, R.M., see Kang-Yih Liou, *J-STQE Jun 95 165-172*
 Jun Wu, see Dennis, T., *J-STQE Sep 95 867-871*

K

- Kaessner, J., see Schell, M., *J-STQE Jun 95 528-534*
 Kai Choong Chan, see Ahmed, K.A., *J-STQE Jun 95 592-600*
 Kajita, M., T. Kawakami, M. Nido, A. Kimura, T. Yoshikawa, K. Kurihara, Y. Sugimoto, and K. Kasahara. Temperature characteristics of a vertical-cavity surface-emitting laser with a broad-gain bandwidth; *J-STQE Jun 95 654-660*
 Kamizato, T., see Shima, A., *J-STQE Jun 95 102-109*
 Kanaev, A.V., see Museur, L., *J-STQE Sep 95 900-907*
 Kang-Yih Liou, M.G. Young, E.C. Burrows, R.M. Jopson, G. Raybon, and C.A. Burrus. High-power broad-area tapered amplifier with a monolithically integrated output focusing lens at 0.98- μm wavelength; *J-STQE Jun 95 165-172*
 Kannari, F., see Yamada, T., *J-STQE Sep 95 891-899*
 Kannari, F., see Inoue, S., *J-STQE Sep 95 908-915*
 Kano, F., see Ishii, H., *J-STQE Jun 95 401-407*
 Kao, Y.-C., see Celii, F.G., *J-STQE Dec 95 1064-1072*
 Karakida, S., see Shima, A., *J-STQE Jun 95 102-109*
 Karin, J.R., see Uskov, A.V., *J-STQE Jun 95 552-561*
 Kasahara, K., see Kajita, M., *J-STQE Jun 95 654-660*
 Kasukawa, A., N. Iwai, N. Yamanaka, and N. Yokouchi. Very high characteristic temperature and constant differential quantum efficiency 1.3- μm GaInAsP-InP strained-layer quantum-well lasers by use of temperature dependent reflectivity (TDR) mirror; *J-STQE Jun 95 293-300*
 Kato, M., see Shima, A., *J-STQE Jun 95 734-740*
 Kato, Y., see Katto, M., *J-STQE Sep 95 924-930*
 Katto, M., M. Okuda, W. Sasaki, K. Kurosawa, and Y. Kato. Electron beam pumped argon-excimer laser using an unstable resonator; *J-STQE Sep 95 924-930*
 Katz, A.J., see Celii, F.G., *J-STQE Dec 95 1064-1072*
 Kawakami, T., see Kajita, M., *J-STQE Jun 95 654-660*
 Kawanaka, J., S. Kubodera, W. Sasaki, K. Kurosawa, K. Mitsuhashi, and T. Igarashi. New xenon excimer lamps excited by quasi-CW jet discharges; *J-STQE Sep 95 852-858*
 Kawano, T., see Uomi, K., *J-STQE Jun 95 203-210*
 Kazarinov, R.F., see Ackerman, D.A., *J-STQE Jun 95 250-263*
 Kazmierski, C., D. Robein, D. Mathoorasing, A. Ougazzaden, and M. Filoche. 1.5- μm DFB lasers with new current-induced gain gratings; *J-STQE Jun 95 371-374*
 Khalifin, V.B., J.M. Arnold, and J.H. Marsh. A theoretical model of synchronization of a mode-locked semiconductor laser with an external pulse stream; *J-STQE Jun 95 523-527*
 Kido, T., N. Kishi, and H. Takahashi. Optical charge-sensing method for testing and characterizing thin-film transistor arrays; *J-STQE Dec 95 993-1001*
 Kikuchi, A., see Yoshida, J., *J-STQE Jun 95 173-182*
 Kim Jong-Seok, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Kim Seung-Hee, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Kimura, A., see Kajita, M., *J-STQE Jun 95 654-660*
 Kinell, D.K., see Feng, Z.C., *J-STQE Dec 95 1119-1125*
 Kishi, N., see Kido, T., *J-STQE Dec 95 993-1001*
 Kishino, K., see Yoshida, J., *J-STQE Jun 95 173-182*
 Kitamura, M., see Jong-In Shim, *J-STQE Jun 95 408-415*
 Kitamura, M., see Jong-In Shim, *J-STQE Jun 95 516-522*

Kizuki, H., *see* Shima, A., *J-STQE Jun 95 102-109*
 Kobayashi, K., *see* Kobayashi, R., *J-STQE Jun 95 723-727*
 Kobayashi, R., H. Hotta, F. Miyasaka, K. Hara, and K. Kobayashi. Real index-guided AlGaInP visible laser with high-bandgap energy AlInP current blocking layer grown by HCl-assisted metalorganic vapor phase epitaxy; *J-STQE Jun 95 723-727*
 Komine, H., J.M. Fukumoto, W.H. Long, Jr., and E.A. Stappaerts. Noncritically phase matched mid-infrared generation in AgGaSe₂; *J-STQE Apr 95 44-49*
 Komori, M., *see* Uomi, K., *J-STQE Jun 95 203-210*
 Kondo, Y., *see* Ishii, H., *J-STQE Jun 95 401-407*
 Korableva, S.L., *see* Sarukura, N., *J-STQE Sep 95 792-804*
 Koren, U., *see* Tessler, N., *J-STQE Jun 95 490-493*
 Kostoulas, Y., *see* Fauchet, P.M., *J-STQE Dec 95 1126-1139*
 Koyama, F., *see* Mukaiyama, T., *J-STQE Jun 95 667-673*
 Kozhevnikov, I.V., *see* Balakireva, L.L., *J-STQE Sep 95 962-969*
 Kozma, L., *see* Kukhlevsky, S.V., *J-STQE Sep 95 941-944*
 Krauss, T.F., R.M. DeLaRue, P.J.R. Laybourn, B. Voegelé, and C.R. Stanley. Efficient semiconductor ring lasers made by a simple self-aligned fabrication process; *J-STQE Jun 95 757-761*
 Krupke, W.F., *see* Marshall, C.D., *J-STQE Apr 95 67-77*
 Krystek, W., *see* Pollak, F.H., *J-STQE Dec 95 1002-1010*
 Kubodera, S., *see* Kawanaka, J., *J-STQE Sep 95 852-858*
 Kubodera, S., *see* Midorikawa, K., *J-STQE Sep 95 931-940*
 Kubota, S., *see* Oka, M., *J-STQE Sep 95 859-866*
 Kukhlevsky, S.V., and L. Kozma. Short-wavelength capillary lasers with tunable spatial coherence; *J-STQE Sep 95 941-944*
 Kumagai, H., *see* Ezaki, M., *J-STQE Sep 95 841-847*
 Kume, M., *see* Yuri, M., *J-STQE Jun 95 473-479*
 Kume, M., *see* Takayama, T., *J-STQE Jun 95 562-568*
 Kunz, R.R., *see* Rothschild, M., *J-STQE Sep 95 916-923*
 Kuphal, E., *see* Hansmann, S., *J-STQE Jun 95 341-345*
 Kurihara, K., *see* Kajita, M., *J-STQE Jun 95 654-660*
 Kuroda, T., *see* Niwa, A., *J-STQE Jun 95 211-217*
 Kurosawa, K., *see* Kawanaka, J., *J-STQE Sep 95 852-858*
 Kurosawa, K., *see* Katto, M., *J-STQE Sep 95 924-930*

L

Langlois, P., *see* Azouz, A., *J-STQE Jun 95 577-582*
 Laybourn, P.J.R., *see* Krauss, T.F., *J-STQE Jun 95 757-761*
 Lear, K.L., *see* Choquette, K.D., *J-STQE Jun 95 661-666*
 Lee, H., *see* Biernacki, P.D., *J-STQE Dec 95 1037-1046*
 Leem Shi-Jong, *see* Won-Jin Choi, *J-STQE Jun 95 717-722*
 Leibenguth, R.E., *see* Choquette, K.D., *J-STQE Jun 95 661-666*
 Leibovitch, M., *see* Pollak, F.H., *J-STQE Dec 95 1002-1010*
 Lenstra, D., *see* Van Tartwijk, G.H.M., *J-STQE Jun 95 466-472*
 Levine, A.M., *see* Van Tartwijk, G.H.M., *J-STQE Jun 95 466-472*
 Lewis, C.L.S., *see* Healy, S.B., *J-STQE Sep 95 949-957*
 Lewis, C.L.S., *see* Healy, S.B., *J-STQE Dec 95 1156*
 Li, G.S., *see* Wu, Y.A., *J-STQE Jun 95 629-637*
 Li, Z.-M., *see* Dion, M., *J-STQE Jun 95 230-233*
 Lien Chuang Shun, *see* Fang, W.-C.W., *J-STQE Jun 95 117-128*
 Lien Chuang Shun, *see* Chih-Sheng Chang, *J-STQE Jun 95 218-229*
 Liew, S.K.C. Above-threshold analysis of three-section DFB/DBR lasers with second-order gratings; *J-STQE Jun 95 363-370*
 Li Guo Ping, *see* Hanh Lu, *J-STQE Jun 95 375-381*
 Ling Yi Liu, *see* Oka, M., *J-STQE Sep 95 859-866*
 Liou Kang-Yih, *see* Kang-Yih Liou, *J-STQE Jun 95 165-172*
 Li Sining, *see* Chi Zhou, *J-STQE Sep 95 872-876*
 Liu Hai-Feng, *see* Ahmed, K.A., *J-STQE Jun 95 592-600*
 Liu Ling Yi, *see* Oka, M., *J-STQE Sep 95 859-866*
 Liu Zhenlin, *see* Sarukura, N., *J-STQE Sep 95 792-804*
 Li Yuelin, *see* Fill, E.E., *J-STQE Sep 95 958-961*
 Logan, R.A., *see* Ackerman, D.A., *J-STQE Jun 95 250-263*
 Long, W.H., Jr., *see* Komine, H., *J-STQE Apr 95 44-49*
 Lopata, J., *see* Passlack, M., *J-STQE Jun 95 110-116*
 Lourtioz, J.-M., *see* Azouz, A., *J-STQE Jun 95 577-582*
 Lowell, J.K., *see* Dadap, J.I., *J-STQE Dec 95 1145-1155*
 Lowery, A.J., *see* Nguyen, L.V.T., *J-STQE Jun 95 494-504*
 Lo Yu-Hwa, *see* Chin-Yi Tsai, *J-STQE Jun 95 316-330*
 Lu, Z.H., A. Majerfeld, P.D. Wright, and L.W. Yang. A comprehensive optical characterization method for high-performance n-p-n AlGaAs-GaAs heterojunction bipolar transistors; *J-STQE Dec 95 1030-1036*
 Lu Hanh, *see* Hanh Lu, *J-STQE Jun 95 375-381*
 Lui, M., *see* McFarlane, R.A., *J-STQE Apr 95 82-91*
 Luryi, S., *see* Portnoi, E.L., *J-STQE Jun 95 451-460*

M

MacDougall, M.H., *see* Hanmin Zhao, *J-STQE Jun 95 196-202*
 Mackechnie, C.J., *see* Pask, H.M., *J-STQE Apr 95 2-13*
 Magari, K., *see* Hillmer, H., *J-STQE Jun 95 356-362*
 Majerfeld, A., *see* Lu, Z.H., *J-STQE Dec 95 1030-1036*
 Makino, T., *see* Evans, J.D., *J-STQE Jun 95 275-284*
 Makino, T., *see* Hanh Lu, *J-STQE Jun 95 375-381*
 Marcenac, D.D., *see* Nowell, M.C., *J-STQE Jun 95 433-441*
 Marconi, M.C., *see* Rocca, J.J., *J-STQE Sep 95 945-948*
 Margalit, M., *see* Tessler, N., *J-STQE Jun 95 490-493*
 Markgraf, S., *see* Pollock, C.R., *J-STQE Apr 95 62-66*
 Marsh, J.H., *see* Portnoi, E.L., *J-STQE Jun 95 451-460*
 Marsh, J.H., *see* Khalfin, V.B., *J-STQE Jun 95 523-527*
 Marshall, C.D., S.A. Payne, L.K. Smith, H.T. Powell, W.F. Krupke, and B.H.T. Chai. 1.047- μ m Yb:Sr₂(PO₄)₃F energy storage optical amplifier; *J-STQE Apr 95 67-77*
 Martins-Filho, J.F., E.A. Avrutin, C.N. Ironside, and J.S. Roberts. Monolithic multiple colliding pulse mode-locked quantum-well lasers, experiment and theory; *J-STQE Jun 95 539-551*
 Mass, J.L., *see* Pollock, C.R., *J-STQE Apr 95 62-66*
 Mathoorasing, D., *see* Kazmiercki, C., *J-STQE Jun 95 371-374*
 Matsui, S., *see* Watanabe, M., *J-STQE Jun 95 728-733*
 Matsushima, Y., *see* Usami, M., *J-STQE Jun 95 244-249*
 Matsuura, H., *see* Watanabe, M., *J-STQE Jun 95 712-716*
 Mawst, L.L., *see* Zmudzinski, C., *J-STQE Jun 95 129-137*
 Ma Zuguang, *see* Chi Zhou, *J-STQE Sep 95 872-876*
 McClary, J., *see* Harned, N., *J-STQE Sep 95 837-840*
 McFarlane, R.A., M. Lui, and D. Yap. Rare earth doped fluoride waveguides fabricated using molecular beam epitaxy; *J-STQE Apr 95 82-91*
 Meney, A.T., D. Prins, A.F. Phillips, J.L. Sly, E.P. O'Reilly, D.J. Dunstan, A.R. Adams, and A. Valster. Determination of the band structure of disordered AlGaInP and its influence on visible-laser characteristics; *J-STQE Jun 95 697-706*
 Merz, J.L., *see* Fouquet, J.E., *J-STQE Dec 95 977-979*
 Mickelson, A.R., *see* Biernacki, P.D., *J-STQE Dec 95 1037-1046*
 Midorikawa, K., Y. Nagata, S. Kubodera, M. Obara, and K. Toyoda. An optical field-induced ionization X-ray laser using a preformed plasma scheme; *J-STQE Sep 95 931-940*
 Miles, R.H., *see* Yong-Hang Zhang, *J-STQE Jun 95 749-756*
 Minch, J.R., *see* Chang, C.-S., *J-STQE Dec 95 1100-1107*
 Mirov, S.B., and T. Basiev. Progress in color center lasers; *J-STQE Apr 95 22-30*
 Mitsuhashi, K., *see* Kawanaka, J., *J-STQE Sep 95 852-858*
 Miyasaka, F., *see* Kobayashi, R., *J-STQE Jun 95 723-727*
 Miyashita, M., *see* Shima, A., *J-STQE Jun 95 102-109*
 Mohrle, M., *see* Sartorius, B., *J-STQE Jun 95 535-538*
 Moise, T.S., *see* Celi, F.G., *J-STQE Dec 95 1064-1072*
 Moller, B., *see* Zeeb, E., *J-STQE Jun 95 616-623*
 Moller-Larsen, A., *see* Salzman, J., *J-STQE Jun 95 346-355*
 Morinaga, M., M. Ishikawa, and N. Suzuki. Analysis on wide continuous wavelength tuning of rapid-tunable quantum-well DFB lasers with carrier-transport effects; *J-STQE Jun 95 427-432*
 Morkoc, H., *see* Grann, E.D., *J-STQE Dec 95 1093-1099*
 Morton, P.A., *see* Ackerman, D.A., *J-STQE Jun 95 250-263*
 Motoda, T., *see* Shima, A., *J-STQE Jun 95 734-740*
 Moulton, P.F., *see* Rines, G.A., *J-STQE Apr 95 50-57*
 Mukaiyama, T., N. Ohnoki, Y. Hayashi, N. Hatori, F. Koyama, and K. Iga. Polarization control of vertical-cavity surface emitting lasers using a birefringent metal/dielectric polarizer loaded on top distributed Bragg reflector; *J-STQE Jun 95 667-673*
 Muser, L., W.Q. Zheng, A.V. Kanaev, and M.C. Castex. A very convenient setup to generate intense VUV coherent light at 125 nm with use of nonlinear effects in mercury vapor at room temperature; *J-STQE Sep 95 900-907*

N

Nabiev, R.F., *see* Zmudzinski, C., *J-STQE Jun 95 129-137*
 Nabiev, R.F., and D. Botez. Comprehensive above-threshold analysis of antiguidded diode laser arrays; *J-STQE Jun 95 138-149*
 Nabiev, R.F., E.C. Vail, and C.J. Chang-Hasnain. Temperature dependent efficiency and modulation characteristics of Al-free 980-nm laser diodes; *J-STQE Jun 95 234-243*
 Nabiev, R.F., *see* Wu, Y.A., *J-STQE Jun 95 629-637*
 Nagai, H., *see* Sato, Y., *J-STQE Sep 95 811-824*
 Nagai, Y., *see* Shima, A., *J-STQE Jun 95 102-109*
 Nagai, Y., *see* Shima, A., *J-STQE Jun 95 734-740*
 Nagarajan, R., *see* Uskova, A.V., *J-STQE Jun 95 552-561*
 Nagata, Y., *see* Midorikawa, K., *J-STQE Sep 95 931-940*
 Nagpal, K.M., *see* Hill, D.E., *J-STQE Jun 95 150-164*
 Naito, H., *see* Yuri, M., *J-STQE Jun 95 473-479*

Naito, H., *see* Takayama, T., *J-STQE Jun 95* 562-568
 Nakajima, K., *see* Delorme, F., *J-STQE Jun 95* 396-400
 Nakano, Y., *see* Sudoh, T.K., *J-STQE Jun 95* 583-591
 Nakata, T., *see* Yamada, T., *J-STQE Sep 95* 891-899
 Nakatsu, H., *see* Watanabe, M., *J-STQE Jun 95* 728-733
 Nakwaski, W., *see* Osinski, M., *J-STQE Jun 95* 681-696
 Naumov, A.K., *see* Sarukura, N., *J-STQE Sep 95* 792-804
 Nesnidal, M., *see* Zmudzinski, C., *J-STQE Jun 95* 129-137
 Nguyen, L.V.T., A.J. Lowery, P.C.R. Gurney, and D. Novak. A time-domain model for high-speed quantum-well lasers including carrier transport effects; *J-STQE Jun 95* 494-504
 Nichols, D.T., *see* Passlack, M., *J-STQE Jun 95* 110-116
 Nido, M., and A. Suzuki. Slow carrier-phonon interaction in InGaAs-InGaAsP multiquantum well investigated by time-development of carrier temperature and gain; *J-STQE Jun 95* 308-315
 Nido, M., *see* Kajita, M., *J-STQE Jun 95* 654-660
 Nishikata, K., *see* Irikawa, M., *J-STQE Jun 95* 285-292
 Nishimura, T., *see* Shima, A., *J-STQE Jun 95* 734-740
 Niwa, A., T. Ohtoshi, and T. Kuroda. Orientation dependence of optical properties in long wavelength strained quantum-well lasers; *J-STQE Jun 95* 211-217
 Nomura, I., *see* Yoshida, J., *J-STQE Jun 95* 173-182
 Norregaard, J., *see* Salzman, J., *J-STQE Jun 95* 346-355
 Novak, D., *see* Nguyen, L.V.T., *J-STQE Jun 95* 494-504
 Nowell, M.C., J.E. Carroll, R.G.S. Plumb, D.D. Marcenac, M.J. Robertson, H. Wickes, and L.M. Zhang. Low-chirp and enhanced-resonant frequency by direct push-pull modulation of DFB lasers; *J-STQE Jun 95* 433-441

O

Obara, M., *see* Arnold, W.H., *J-STQE Sep 95* 765-767
 Obara, M., *see* Ezaki, M., *J-STQE Sep 95* 841-847
 Obara, M., *see* Midorikawa, K., *J-STQE Sep 95* 931-940
 Ohnoki, N., *see* Mukaihara, T., *J-STQE Jun 95* 667-673
 Ohtoshi, T., *see* Niwa, A., *J-STQE Jun 95* 211-217
 Oishi, A., *see* Uomi, K., *J-STQE Jun 95* 203-210
 Oka, A., *see* Uomi, K., *J-STQE Jun 95* 203-210
 Oka, M., Ling Yi Liu, W. Wiechmann, N. Eguchi, and S. Kubota. All solid-state continuous-wave frequency-quadrupled Nd:YAG laser; *J-STQE Sep 95* 859-866
 Okai, M., M. Suzuki, and M. Aoki. Complex-coupled $\lambda/4$ -shifted DFB lasers with a flat FM response; *J-STQE Jun 95* 461-465
 Okuda, H., *see* Watanabe, M., *J-STQE Jun 95* 712-716
 Okuda, M., *see* Katto, M., *J-STQE Sep 95* 924-930
 Olesen, H., *see* Salzman, J., *J-STQE Jun 95* 346-355
 Olesen, H., *see* Jong-In Shim, *J-STQE Jun 95* 516-522
 Omura, E., *see* Shima, A., *J-STQE Jun 95* 102-109
 Omura, E., *see* Shima, A., *J-STQE Jun 95* 734-740
 Onomura, M., *see* Tohyama, M., *J-STQE Jun 95* 416-426
 O'Reilly, E.P., *see* Mcney, A.T., *J-STQE Jun 95* 697-706
 Osinski, M., and W. Nakwaski. Thermal analysis of closely-packed two-dimensional etched-well surface-emitting laser arrays; *J-STQE Jun 95* 681-696
 Ostdiek, P.H., *see* Sun, D., *J-STQE Jun 95* 674-680
 Otsubo, M., *see* Shima, A., *J-STQE Jun 95* 102-109
 Otsubo, M., *see* Shima, A., *J-STQE Jun 95* 734-740
 Ougazzaden, A., *see* Kazmierski, C., *J-STQE Jun 95* 371-374

P

Palmateer, S.C., *see* Rothschild, M., *J-STQE Sep 95* 916-923
 Pask, H.M., R.J. Carman, D.C. Hanna, A.C. Tropper, C.J. Mackechnie, P.R. Barber, and J.M. Dawes. Ytterbium-doped silica fiber lasers: versatile sources for the 1-1.2 μm region; *J-STQE Apr 95* 2-13
 Passlack, M., C.G. Bethea, W.S. Hobson, J. Lopata, E.F. Schubert, G.J. Zydzik, D.T. Nichols, J.F. de Jong, U.K. Chakrabarti, and N.K. Dutta. Infrared microscopy studies on high-power InGaAs-GaAs-InGaP lasers with Ga_2O_3 facet coatings; *J-STQE Jun 95* 110-116
 Payne, S.A., *see* Marshall, C.D., *J-STQE Apr 95* 67-77
 Peard, K.A., *see* Tobin, R.C., *J-STQE Sep 95* 805-810
 Peng, C., *see* Fauchet, P.M., *J-STQE Dec 95* 1126-1139
 Perkowitz, S., *see* Feng, Z.C., *J-STQE Dec 95* 1119-1125
 Pert, G.J., *see* Healy, S.B., *J-STQE Sep 95* 949-957
 Pert, G.J., *see* Healy, S.B., *J-STQE Dec 95* 1156
 Petermann, K. External optical feedback phenomena in semiconductor lasers; *J-STQE Jun 95* 480-489
 Peters, M.G., *see* Scott, J.W., *J-STQE Jun 95* 638-648
 Phillips, A.F., *see* Mcney, A.T., *J-STQE Jun 95* 697-706
 Ping Li Guo, *see* Hanh Lu, *J-STQE Jun 95* 375-381

Pinto, J.F., L. Esterowitz, and G.H. Rosenblatt. Frequency tripling of a Q-switched Cr:LiSAF laser to the UV region; *J-STQE Apr 95* 58-61
 Piper, J.A., *see* Glover, A.C.J., *J-STQE Sep 95* 830-836
 Plowes, J.A., *see* Healy, S.B., *J-STQE Sep 95* 949-957
 Plowes, J.A., *see* Healy, S.B., *J-STQE Dec 95* 1156
 Plumb, R.G.S., *see* Nowell, M.C., *J-STQE Apr 95* 433-441
 Pollak, F.H., W. Krystek, M. Leibovitch, M.L. Gray, and W.S. Hobson. Contactless electromodulation for the nondestructive, room-temperature analysis of wafer-sized semiconductor device structures; *J-STQE Dec 95* 1002-1010
 Pollock, C.R., D.B. Barber, J.L. Mass, and S. Markgraf. Cr⁴⁺ lasers: present performance and prospects for new host lattices; *J-STQE Apr 95* 62-66
 Portnoi, E.L., V.B. Gorfinkel, E.A. Avrutin, I.G. Thaync, D.A. Barrow, J.H. Marsh, and S. Luryi. Optoelectronic microwave-range frequency mixing in semiconductor lasers; *J-STQE Jun 95* 451-460
 Powell, H.T., *see* Marshall, C.D., *J-STQE Apr 95* 673-77
 Pretzler, G., *see* Fill, E.E., *J-STQE Sep 95* 958-961
 Prins, D., *see* Mcney, A.T., *J-STQE Jun 95* 697-706
 Prokes, S.M. Spectroscopic study of red light emission in porous silicon; *J-STQE Dec 95* 1140-1144
 Puetz, N., *see* Evans, J.D., *J-STQE Jun 95* 275-284

Q

Qi Wang, *see* Chi Zhou, *J-STQE Sep 95* 872-876

R

Ramdane, A., *see* Delorme, F., *J-STQE Jun 95* 396-400
 Raybon, G., *see* Kang-Yih Liou, *J-STQE Jun 95* 165-172
 Reiner, C., *see* Zeeb, E., *J-STQE Jun 95* 616-623
 Ries, M., *see* Zeeb, E., *J-STQE Jun 95* 616-623
 Rines, G.A., H.H. Zenzie, R.A. Schwarz, Y. Isyanova, and P.F. Moulton. Nonlinear conversion of Ti:sapphire laser wavelengths; *J-STQE Apr 95* 50-57
 Robein, D., *see* Kazmierski, C., *J-STQE Jun 95* 371-374
 Roberts, J.S., *see* Martins-Filho, J.F., *J-STQE Jun 95* 539-551
 Robertson, M.J., *see* Nowell, M.C., *J-STQE Jun 95* 433-441
 Rocca, J.J., M.C. Marconi, J.L.A. Chilla, D.P. Clark, F.G. Tomasel, and V.N. Shlyaptshev. Discharge-driven 46.9-nm amplifier with gain-length approaching saturation; *J-STQE Sep 95* 945-948
 Rose, B., *see* Delorme, F., *J-STQE Jun 95* 396-400
 Rosenblatt, G.H., *see* Pinto, J.F., *J-STQE Apr 95* 58-61
 Ross, D., *see* Dion, M., *J-STQE Jun 95* 230-233
 Rothschild, M., A.R. Forte, M.W. Horn, R.R. Kunz, S.C. Palmateer, and J.H.C. Sedlacek. 193-nm lithography; *J-STQE Sep 95* 916-923
 Rozsa, K., *see* Tobin, R.C., *J-STQE Sep 95* 805-810
 Russell, N.M., *see* Dadap, J.I., *J-STQE Dec 95* 1145-1155

S

Sagawa, M., T. Toyonaka, K. Hiramoto, K. Shinoda, and K. Uomi. High-power highly-reliable operation of 0.98- μm InGaAs-InGaP strain-compensated single-quantum-well lasers with tensile-strained InGaAsP barriers; *J-STQE Jun 95* 189-194
 Saito, Y., *see* Sato, Y., *J-STQE Sep 95* 811-824
 Salvador, A., *see* Grann, E.D., *J-STQE Dec 95* 1093-1099
 Salzman, J., H. Olesen, A. Moller-Larsen, O. Albrektsen, J. Hanberg, J. Norregaard, B. Jonsson, and B. Tromborg. Distributed feedback lasers with an S-bent waveguide for high-power single-mode operation; *J-STQE Jun 95* 346-355
 Samarth, N., *see* Crooker, S.A., *J-STQE Dec 95* 1082-1092
 Sampson, D.D., *see* Griffin, R.A., *J-STQE Jun 95* 569-576
 Sartorius, B., M. Mohrle, and U. Feiste. 12-64 GHz continuous frequency tuning in self-pulsating 1.55- μm multiquantum-well DFB lasers; *J-STQE Jun 95* 535-538
 Sarukura, N., M.A. Dubinskii, Zhenlin Liu, V.V. Semashko, A.K. Naumov, S.L. Korableva, R.Y. Abdulsabirov, K. Edamatsu, Y. Suzuki, T. Itoh, and Y. Segawa. Ce³⁺-activated fluoride crystals as prospective active media for widely tunable ultraviolet ultrafast lasers with direct 10-ns pumping; *J-STQE Sep 95* 792-804
 Sasaki, K., *see* Watanabe, M., *J-STQE Jun 95* 728-733
 Sasaki, W., *see* Kawanaka, J., *J-STQE Sep 95* 852-858
 Sasaki, W., *see* Katto, M., *J-STQE Sep 95* 924-930
 Sato, T., *see* Seki, H., *J-STQE Sep 95* 825-829
 Sato, Y., M. Inoue, S. Fujikawa, Y. Saito, A. Suzuki, K. Haruta, and H. Nagai. Development of a 2-kW XeCl laser with a surface corona preionization scheme and a spiker-sustainer circuit; *J-STQE Sep 95* 811-824

- Schell, M., D. Huhse, W. Utz, J. Kaessner, D. Bimberg, and I.S. Tarasov. Jitter and dynamics of self-seeded Fabry-Perot laser diodes; *J-STQE Jun 95* 528-534
- Schneider, R.P., see Choquette, K.D., *J-STQE Jun 95* 661-666
- Schneider, R.P., Jr., see Chow, W.W., *J-STQE Jun 95* 649-653
- Schubert, E.F., see Passlack, M., *J-STQE Jun 95* 110-116
- Schwarz, R.A., see Rines, G.A., *J-STQE Apr 95* 50-57
- Scott, J.W., D.B. Young, B.J. Thibault, M.G. Peters, and L.A. Coldren. Design of index-guided vertical-cavity lasers for low temperature-sensitivity, sub-milliamp thresholds, and single-mode operation; *J-STQE Jun 95* 638-648
- Sedlacek, J.H.C., see Rothschild, M., *J-STQE Sep 95* 916-923
- Segawa, Y., see Sarukura, N., *J-STQE Sep 95* 792-804
- Seki, H., S. Takemori, and T. Sato. Development of a highly efficient nitrogen laser using an ultra-fast magnetic pulse compression circuit; *J-STQE Sep 95* 825-829
- Seki, S., K. Yokoyama, and P. Sotirelis. Theoretical analysis of high-temperature characteristics of 1.3- μm InP-based quantum-well lasers; *J-STQE Jun 95* 264-274
- Semashko, V.V., see Sarukura, N., *J-STQE Sep 95* 792-804
- Sentis, M.L., see Tischler, H., *J-STQE Sep 95* 877-885
- Sentis, M.L., see Tischler, H., *J-STQE Sep 95* 886-890
- Seung-Hee Kim, see Won-Jin Choi, *J-STQE Jun 95* 717-722
- Shamaly, J.J., see Harned, N., *J-STQE Sep 95* 837-840
- Sheih, S., see Grann, E.D., *J-STQE Dec 95* 1093-1099
- Shighihara, K., see Shima, A., *J-STQE Jun 95* 102-109
- Shi-Jong Leem, see Won-Jin Choi, *J-STQE Jun 95* 717-722
- Shima, A., H. Kizuki, A. Takemoto, S. Karakida, M. Miyashita, Y. Nagai, T. Kamizato, K. Shighihara, A. Adachi, E. Omura, and M. Otsubo. 0.78- and 0.98- μm ridge-waveguide lasers buried with AlGaAs confinement layer selectively grown by chloride-assisted MOCVD; *J-STQE Jun 95* 102-109
- Shima, A., M. Kato, Y. Nagai, T. Motoda, T. Nishimura, E. Omura, and M. Otsubo. Uniform and high-power characteristics of AlGaInP visible laser diodes and their four-element arrays fabricated on a three-inch ϕ wafer; *J-STQE Jun 95* 734-740
- Shimada, N., see Watanabe, M., *J-STQE Jun 95* 712-716
- Shimizu, H., see Irikawa, M., *J-STQE Jun 95* 285-292
- Shim Jong-In, see Jong-In Shim, *J-STQE Jun 95* 408-415
- Shim Jong-In, see Jong-In Shim, *J-STQE Jun 95* 516-522
- Shinoda, K., see Sagawa, M., *J-STQE Jun 95* 189-194
- Shiyaptev, V.N., see Rocca, J.J., *J-STQE Sep 95* 945-948
- Shtengel, G.E., see Ackerman, D.A., *J-STQE Jun 95* 250-263
- Shun Lien Chuang, see Fang, W.-C.W., *J-STQE Jun 95* 117-128
- Shun Lien Chuang, see Chih-Sheng Chang, *J-STQE Jun 95* 218-229
- Simmons, J.G., see Evans, J.D., *J-STQE Jun 95* 275-284
- Sining Li, see Chi Zhou, *J-STQE Sep 95* 872-876
- Slempkes, S., see Delorme, F., *J-STQE Jun 95* 396-400
- Sly, J.L., see Meney, A.T., *J-STQE Jun 95* 697-706
- Smith, L.K., see Marshall, C.D., *J-STQE Apr 95* 67-77
- Smith, P.B., W.M. Duncan, and A.A. Allerman. Optical characterization of heterojunction bipolar transistors; *J-STQE Dec 95* 1011-1016
- Smowton, P., see Blood, P., *J-STQE Jun 95* 707-711
- Sotirelis, P., see Seki, S., *J-STQE Jun 95* 264-274
- Spence, D.E., and C.L. Tang. Characterization and applications of high repetition rate, broadly tunable, femtosecond optical parametric oscillators; *J-STQE Apr 95* 31-43
- Spencer, R.M., see Chin-Yi Tsai, *J-STQE Jun 95* 316-330
- Stanley, C.R., see Krauss, T.F., *J-STQE Jun 95* 757-761
- Stappaerts, E.A., see Komine, H., *J-STQE Apr 95* 44-49
- Stelmakh, N., see Azouz, A., *J-STQE Jun 95* 577-582
- Stoneman, R.C., and L. Esterowitz. Efficient 1.94- μm Tm:YALO laser; *J-STQE Apr 95* 78-81
- Stulen, R.H. 13-nm extreme ultraviolet lithography; *J-STQE Sep 95* 970-975
- Suda, D.A., see Bewtra, N., *J-STQE Jun 95* 331-340
- Sudoh, T.K., M. Funabashi, Y. Nakano, K. Tada, and T. Hirata. Dynamics of gain-switching operation in gain-coupled distributed-feedback semiconductor lasers with absorptive grating; *J-STQE Jun 95* 583-591
- Sugimoto, Y., see Kajita, M., *J-STQE Jun 95* 654-660
- Sun, D., E. Towe, P.H. Ostdiek, J.W. Grantham, and G.J. Vansuch. Polarization control of vertical-cavity surface-emitting lasers through use of an anisotropic gain distribution in [110]-oriented strained quantum-well structures; *J-STQE Jun 95* 674-680
- Suzuki, A., see Nido, M., *J-STQE Jun 95* 308-315
- Suzuki, A., see Sato, Y., *J-STQE Sep 95* 811-824
- Suzuki, M., see Okai, M., *J-STQE Jun 95* 461-465
- Suzuki, N., see Tohyama, M., *J-STQE Jun 95* 416-426
- Suzuki, N., see Morinaga, M., *J-STQE Jun 95* 427-432
- Suzuki, Y., see Sarukura, N., *J-STQE Sep 95* 792-804
- Szalai, L., see Tobin, R.C., *J-STQE Sep 95* 805-810

T

- Tabatabaie, N., see Zhang, T., *J-STQE Jun 95* 606-615
- Tada, K., see Sudoh, T.K., *J-STQE Jun 95* 583-591
- Tae-Kyung Yoo, see Won-Jin Choi, *J-STQE Jun 95* 717-722
- Takahashi, H., see Kido, T., *J-STQE Dec 95* 993-1001
- Takahashi, K., see Watanabe, M., *J-STQE Jun 95* 728-733
- Takahashi, Y., see Usami, M., *J-STQE Jun 95* 244-249
- Takakuwa, C., see Tohyama, M., *J-STQE Jun 95* 416-426
- Takayama, T., see Yuri, M., *J-STQE Jun 95* 473-479
- Takayama, T., O. Imafuji, M. Yuri, H. Naito, M. Kume, A. Yoshikawa, and K. Itoh. 800 mW peak-power self-sustained pulsation GaAlAs laser diodes; *J-STQE Jun 95* 562-568
- Takemori, S., see Seki, H., *J-STQE Sep 95* 825-829
- Takemoto, A., see Shima, A., *J-STQE Jun 95* 102-109
- Tamamura, T., see Ishii, H., *J-STQE Jun 95* 401-407
- Tan, G.L., see Bewtra, N., *J-STQE Jun 95* 331-340
- Tanbun-Ek, T., see Ackerman, D.A., *J-STQE Jun 95* 250-263
- Tanbun-Ek, T., see Chang, C.-S., *J-STQE Dec 95* 1100-1107
- Tang, C.L., see Spence, D.E., *J-STQE Apr 95* 31-43
- Tani, K., see Watanabe, M., *J-STQE Jun 95* 728-733
- Tarasov, I.S., see Schell, M., *J-STQE Jun 95* 528-534
- Templeton, I., see Fallahi, M., *J-STQE Jun 95* 382-386
- Tessler, N., M. Margalit, G. Eisenstein, and U. Koren. Wide-band amplitude modulation by electrooptic tuning of the center wavelength in short-cavity distributed Bragg reflector lasers; *J-STQE Jun 95* 490-493
- Thayne, I.G., see Portnoi, E.L., *J-STQE Jun 95* 451-460
- Thibault, B.J., see Scott, J.W., *J-STQE Jun 95* 638-648
- Thompson, D.A., see Evans, J.D., *J-STQE Jun 95* 275-284
- Thompson, J., see Fallahi, M., *J-STQE Jun 95* 382-386
- Tischler, H., P. Delaporte, B. Fontaine, and M.L. Sentis. Vacuum ultraviolet emissions from the ionic excimer molecules (KrCs)⁺ and (HeAr)⁺ by low-energy electron-beam excitation; *J-STQE Sep 95* 877-885
- Tischler, H., P. Delaporte, and M.L. Sentis. Investigations on the VUV emissions of Ne-Xe-Cs gas mixtures excited by an electrical discharge; *J-STQE Sep 95* 886-890
- Tobin, R.C., K.A. Peard, G.H. Bode, K. Rozsa, Z. Donko, and L. Szalai. High-gain hollow-cathode metal ion lasers for the UV and VUV; *J-STQE Sep 95* 805-810
- Tohmori, Y., see Ishii, H., *J-STQE Jun 95* 401-407
- Tohyama, M., M. Funemizu, M. Onomura, C. Takakuwa, and N. Suzuki. Mechanism of wavelength tuning and frequency modulation in three-electrode DFB lasers; *J-STQE Jun 95* 416-426
- Tomasel, F.G., see Rocca, J.J., *J-STQE Sep 95* 945-948
- Toth, C., see Dennis, T., *J-STQE Sep 95* 867-871
- Towe, E., see Sun, D., *J-STQE Jun 95* 674-680
- Towe, E., see Goldberg, B.B., *J-STQE Dec 95* 1073-1081
- Toyoda, K., see Ezaki, M., *J-STQE Sep 95* 841-847
- Toyoda, K., see Midorikawa, K., *J-STQE Sep 95* 931-940
- Toyonaka, T., see Sagawa, M., *J-STQE Jun 95* 189-194
- Tromborg, B., see Salzman, J., *J-STQE Jun 95* 346-355
- Tropper, A.C., see Pask, H.M., *J-STQE Apr 95* 2-13
- Tsai Chin-Yao, see Chin-Yi Tsai, *J-STQE Jun 95* 316-330
- Tsai Chin-Yi, see Chin-Yi Tsai, *J-STQE Jun 95* 316-330
- Tsen, K.T., see Grann, E.D., *J-STQE Dec 95* 1093-1099
- Tsuchiya, T., see Uomi, K., *J-STQE Jun 95* 203-210
- Tsujihara, K., see Hanabusa, M., *J-STQE Sep 95* 848-851
- Tsybeskov, L., see Fauchet, P.M., *J-STQE Dec 95* 1126-1139
- Tucker, R.S., see Botez, D., *J-STQE Jun 95* 100-101
- Tucker, R.S., see Ahmed, Z., *J-STQE Jun 95* 505-515

U

- Uchida, A., see Yamada, T., *J-STQE Sep 95* 891-899
- Ueno, Y., see Inoue, S., *J-STQE Sep 95* 908-915
- Unlu, M.S., see Goldberg, B.B., *J-STQE Dec 95* 1073-1081
- Uomi, K., see Sagawa, M., *J-STQE Jun 95* 189-194
- Uomi, K., T. Tsuchiya, M. Komori, A. Oka, T. Kawano, and A. Oishi. Ultralow threshold 1.3- μm InGaAsP-InP compressive-strained multiquantum-well monolithic laser array for parallel high-density optical interconnects; *J-STQE Jun 95* 203-210
- Uppal, K., see Hanmin Zhao, *J-STQE Jun 95* 196-202
- Usami, M., Y. Matsushima, and Y. Takahashi. 0.98- μm InGaAs-InGaP strained quantum-well lasers with GaAs-InGaP superlattice optical confinement layer; *J-STQE Jun 95* 244-249
- Uskov, A.V., J.R. Karin, R. Nagarajan, and J.E. Bowers. Dynamics of carrier heating and sweepout in waveguide saturable absorbers; *J-STQE Jun 95* 552-561
- Utz, W., see Schell, M., *J-STQE Jun 95* 528-534

V

- Vail, E.C., see Nabiev, R.F., *J-STQE Jun 95 234-243*
 Valster, A., see Meney, A.T., *J-STQE Jun 95 697-706*
 Vandyshev, J.M.V., see Fauchet, P.M., *J-STQE Dec 95 1126-1139*
 van Exter, M.P., A.K. Jansen Van Doorn, and J.P. Woerdman. Effect of spatial filtering on the spontaneous emission spectrum of a sub-threshold VCSEL; *J-STQE Jun 95 601-605*
 Vansuch, G.J., see Sun, D., *J-STQE Jun 95 674-680*
 Van Tartwijk, G.H.M., A.M. Levine, and D. Lenstra. Sisyphus effect in semiconductor lasers with optical feedback; *J-STQE Jun 95 466-472*
 Voegelé, B., see Krauss, T.F., *J-STQE Jun 95 757-761*
 von Behren, J., see Fauchet, P.M., *J-STQE Dec 95 1126-1139*

W

- Walter, H., see Hansmann, S., *J-STQE Jun 95 341-345*
 Wang Qi, see Chi Zhou, *J-STQE Sep 95 872-876*
 Watanabe, M., H. Matsuura, N. Shimada, and H. Okuda. Optimum tensile-strained multi-quantum-well structure of 630-nm band InGaAlP lasers for high temperature and reliable operation; *J-STQE Jun 95 712-716*
 Watanabe, M., K. Tani, K. Takahashi, K. Sasaki, H. Nakatsu, M. Hosoda, S. Matsui, O. Yamamoto, and S. Yamamoto. Fundamental-transverse-mode high-power AlGaInP laser diode with windows grown on facets; *J-STQE Jun 95 728-733*
 Waynant, R., see Arnold, W.H., *J-STQE Sep 95 765-767*
 Weiser, G., see Jaeger, A., *J-STQE Dec 95 1113-1118*
 Whitney, R.L., see Feng, Z.C., *J-STQE Dec 95 1119-1125*
 Wickes, H., see Nowell, M.C., *J-STQE Jun 95 433-441*
 Wiechmann, W., see Oka, M., *J-STQE Sep 95 859-866*
 Wiedemann, P., see Jaeger, A., *J-STQE Dec 95 1113-1118*
 Williams, R.L., see Dion, M., *J-STQE Jun 95 230-233*
 Withford, M.J., and D.J.W. Brown. Improved ultraviolet second-harmonic generation at elevated repetition rates from a medium-scale copper-vapor laser; *J-STQE Sep 95 779-783*
 Woerdman, J.P., see van Exter, M.P., *J-STQE Jun 95 601-605*
 Wohlbiel, J.G., see Zhang, T., *J-STQE Jun 95 606-615*
 Wolf, T., see Amann, M.-C., *J-STQE Jun 95 387-395*
 Won-Jin Choi, Ji-Ho Chang, Won-Taek Choi, Seung-Hee Kim, Jong-Seok Kim, Shi-Jong Leem, and Tae-Kyung Yoo. Hydrogen effect on 670-nm AlGaInP visible laser during high temperature operation; *J-STQE Jun 95 717-722*
 Won-Taek Choi, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Wright, P.D., see Lu, Z.H., *J-STQE Dec 95 1030-1036*
 Wu, Y.A., G.S. Li, R.F. Nabiev, K.D. Choquette, C. Caneau, and C.J. Chang-Hasnain. Single-mode, passive antiguide vertical cavity surface emitting laser; *J-STQE Jun 95 629-637*
 Wu Jun, see Dennis, T., *J-STQE Sep 95 867-871*
 Wupen Yuen, see Eng, L.E., *J-STQE Jun 95 624-628*

X

- Xu, J.M., see Bewtra, N., *J-STQE Jun 95 331-340*

Y

- Yamada, T., A. Uchida, T. Nakata, and F. Kannari. Subpicosecond pulse compression in the VUV region by induced-phase modulation in Xe; *J-STQE Sep 95 891-899*
 Yamaguchi, M., see Jong-In Shim, *J-STQE Jun 95 408-415*
 Yamaguchi, M., see Jong-In Shim, *J-STQE Jun 95 516-522*
 Yamamoto, O., see Watanabe, M., *J-STQE Jun 95 728-733*
 Yamamoto, S., see Watanabe, M., *J-STQE Jun 95 728-733*
 Yamanaka, N., see Kasukawa, A., *J-STQE Jun 95 293-300*
 Yamazaki, H., see Jong-In Shim, *J-STQE Jun 95 516-522*
 Yang, L.W., see Lu, Z.H., *J-STQE Dec 95 1030-1036*
 Yang Gye-Mo, see Hanmin Zhao, *J-STQE Jun 95 196-202*
 Yap, D., see McFarlane, R.A., *J-STQE Apr 95 82-91*
 Yi Liu Ling, see Oka, M., *J-STQE Sep 95 859-866*
 Yokouchi, N., see Kasukawa, A., *J-STQE Jun 95 293-300*
 Yokoyama, K., see Seki, S., *J-STQE Jun 95 264-274*
 Yong Cheng, see Hanmin Zhao, *J-STQE Jun 95 196-202*
 Yong-Hang Zhang, R.H. Miles, and D.H. Chow. InAs-InAs_xSb_{1-x} type-II superlattice midwave infrared lasers grown on InAs substrates; *J-STQE Jun 95 749-756*
 Yoo Tae-Kyung, see Won-Jin Choi, *J-STQE Jun 95 717-722*
 Yoshida, J., K. Kishino, A. Kikuchi, and I. Nomura. Continuous-Wave (CW) operation of GaInP-AlGaInP visible compressively strained multiple quantum-wire (CS-WQWR) lasers; *J-STQE Jun 95 173-182*

+ Check author entry for coauthors

- Yoshikawa, A., see Takayama, T., *J-STQE Jun 95 562-568*
 Yoshikawa, T., see Kajita, M., *J-STQE Jun 95 654-660*
 Yoshikuni, Y., see Ishii, H., *J-STQE Jun 95 401-407*
 Young, D.B., see Scott, J.W., *J-STQE Jun 95 638-648*
 Young, J.F., see Dennis, T., *J-STQE Sep 95 867-871*
 Young, M.G., see Kang-Yih Liou, *J-STQE Jun 95 165-172*
 Yuelin Li, see Fill, E.E., *J-STQE Sep 95 958-961*
 Yuen Wupen, see Eng, L.E., *J-STQE Jun 95 624-628*
 Yu-Hwa Lo, see Chin-Yi Tsai, *J-STQE Jun 95 316-330*
 Yuri, M., S. Harris, Jr., T. Takayama, O. Imafuji, H. Naito, M. Kume, K. Itoh, and T. Baba. Two-dimensional analysis of self-sustained pulsation for narrow-stripe AlGaAs lasers; *J-STQE Jun 95 473-479*
 Yuri, M., see Takayama, T., *J-STQE Jun 95 562-568*

Z

- Zeeb, E., B. Moller, C. Reiner, M. Ries, T. Hackbarth, and K.J. Ebeling. Planar proton implanted VCSEL's and fiber-coupled 2-D VCSEL arrays; *J-STQE Jun 95 616-623*
 Zenzie, H.H., see Rines, G.A., *J-STQE Apr 95 50-57*
 Zhang, L.M., see Nowell, M.C., *J-STQE Jun 95 433-441*
 Zhang, T., J.G. Wohlbiel, K.D. Choquette, and N. Tabatabaie. Microcavity vacuum-field configuration and the spontaneous emission power; *J-STQE Jun 95 606-615*
 Zhang Guodong, see Guodong Zhang, *J-STQE Jun 95 183-188*
 Zhang Yong-Hang, see Yong-Hang Zhang, *J-STQE Jun 95 749-756*
 Zhao Hanmin, see Hanmin Zhao, *J-STQE Jun 95 196-202*
 Zheng, W.Q., see Museur, L., *J-STQE Sep 95 900-907*
 Zhenlin Liu, see Sarukura, N., *J-STQE Sep 95 792-804*
 Zhou Chi, see Chi Zhou, *J-STQE Sep 95 872-876*
 Zhu, H.-L., see Hillmer, H., *J-STQE Jun 95 356-362*
 Zmudzinski, C., D. Botez, L.I. Mawst, A. Bhattacharya, M. Nesnidal, and R.F. Nabiev. Three-core ARROW-type diode laser: novel high-power, single-mode device, and effective master oscillator for flared antiguided MOPA's; *J-STQE Jun 95 129-137*
 Zuguang Ma, see Chi Zhou, *J-STQE Sep 95 872-876*
 Zydzik, G.J., see Passlack, M., *J-STQE Jun 95 110-116*

SUBJECT INDEX

A

- Ablation**
 C, diamond-like films, excimer laser deposition using frozen acetylene. Hanabusa, M., +, *J-STQE Sep 95 848-851*
 CdTe-doped PTFE thin films, laser deposition. Inoue, S., +, *J-STQE Sep 95 908-915*
- Aluminum materials/devices**
 AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. Zhang, T., +, *J-STQE Jun 95 606-615*
 AlGaAs narrow-stripe lasers, self-sustained pulsation. Yuri, M., +, *J-STQE Jun 95 473-479*
 AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. Shima, A., +, *J-STQE Jun 95 102-109*
 AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. Azouz, A., +, *J-STQE Jun 95 577-582*
 AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. van Exter, M.P., +, *J-STQE Jun 95 601-605*
 AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. Watanabe, M., +, *J-STQE Jun 95 728-733*
 AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. Kobayashi, R., +, *J-STQE Jun 95 723-727*
 AlGaInP VCSEL, threshold current minimization. Chow, W.W., +, *J-STQE Jun 95 649-653*
 AlGaInP vis. laser, H effect, high temp. operation. Won-Jin Choi, +, *J-STQE Jun 95 717-722*
 AlGaInP vis. LD and arrays, fab., high-power charact. Shima, A., +, *J-STQE Jun 95 734-740*
 GaAlAs LD, 800 mW peak-power self-sustained pulsation. Takayama, T., +, *J-STQE Jun 95 562-568*
 GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. Eng, L.E., +, *J-STQE Jun 95 624-628*
 GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. Osinski, M., +, *J-STQE Jun 95 681-696*
 GaAs-AlGaAs MQW GRINSLCH laser temp. sensitivity. Dion, M., +, *J-STQE Jun 95 230-233*
 GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. Uskov, A.V., +, *J-STQE Jun 95 552-561*

† Check author entry for subsequent corrections/comments

- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292
- GaN_{0.5}P-AlGaN_{0.5}P quantum well vis. laser, band struct. determ. *Meney, A.T.*, +, *J-STQE Jun 95* 697-706
- GaN_{0.5}P-AlGaN_{0.5}P vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182
- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95* 712-716
- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao*, +, *J-STQE Jun 95* 196-202
- InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
- LiCaAlF₆:Ce³⁺, tunable UV ultrafast lasers, direct pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- LiSrAlF₆:Cr laser, Q-switched, SHG. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61
- Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57
- ZBLAN:Nd fiber laser in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- Amplifier noise; cf. Laser noise**
- Amplifiers; cf. Laser amplifiers; Power amplifiers**
- Argon materials/devices**
- Ar²⁺F⁺ ionic excimers, VUV spectra. *Chi Zhou*, +, *J-STQE Sep 95* 872-876
- discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95* 945-948
- excimer laser, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
- Arrays**
- thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95* 993-1001
- B**
- Barium materials/devices**
- BaB₂O₄ cryst. harmonic generation of Ti:sapphire laser wavelengths. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57
- β-BaB₂O₄, intracavity freq. doubled CW Nd:YAG laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- ZBLAN:Nd fiber laser in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- Beams; cf. Gaussian beams**
- Biomedical applications of optical radiation; cf. Laser biomedical applications**
- Bipolar transistors; cf. Heterojunction bipolar transistors**
- Birefringence**
- DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
- InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673
- Bragg scattering; cf. Distributed Bragg reflector lasers**
- C**
- Cadmium materials/devices**
- CdTe-doped PTFE thin films, laser deposition. *Inoue, S.*, +, *J-STQE Sep 95* 908-915
- laser-prod. plasma target materials for Xe²⁺ Auger laser pumping. *Dennis, T.*, +, *J-STQE Sep 95* 867-871
- Calcium materials/devices**
- LiCaAlF₆:Ce³⁺, tunable UV ultrafast lasers, direct pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- Carbon materials/devices**
- CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
- diamond-like C films, excimer laser deposition, frozen acetylene. *Hanabusa, M.*, +, *J-STQE Sep 95* 848-851
- Carrier processes; cf. Charge carrier processes**
- Cerium materials/devices**
- Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- Cesium materials/devices**
- Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
- Chaos**
- semicond. lasers, external opt. feedback phenom. *Petermann, K.*, *J-STQE Jun 95* 480-489
- Charge carrier processes**
- 1.3 μm semicond. lasers, gain anal. in T₀ determination. *Ackerman, D.A.*, +, *J-STQE Jun 95* 250-263
- AlGaAs-based p-i-n nanostruct. semicond., nonequilib. electron distrib. and high-field transport, picosecond Raman probe. *Grann, E.D.*, +, *J-STQE Dec 95* 1093-1099
- antiguided diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95* 138-149
- corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95* 1156
- GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V.*, +, *J-STQE Jun 95* 552-561
- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292
- Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95* 949-957
- InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95* 234-243
- InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95* 308-315
- InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim*, +, *J-STQE Jun 95* 408-415
- InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95* 638-648
- InP-based 1.3-μm QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95* 264-274
- quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N.*, +, *J-STQE Jun 95* 331-340
- rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95* 427-432
- semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W.*, +, *J-STQE Jun 95* 117-128
- semicond. quantum well laser, carrier transport, nonlin. gain coeffs. *Chin-Yi Tsai*, +, *J-STQE Jun 95* 316-330
- strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang*, +, *J-STQE Jun 95* 218-229
- three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95* 416-426
- Charge carrier processes; cf. Space charge**
- Chemical vapor deposition; cf. CVD**
- Chirp modulation**
- AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582
- DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
- DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
- direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95* 433-441
- GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wavelength. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628
- Chromium materials/devices**
- Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61
- CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
- Cr⁴⁺:doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95* 62-66
- Circuits; cf. Equivalent circuits**
- Collision processes; cf. Particle collisions**
- Communication equipment; cf. Optical communication equipment**
- Computer architecture; cf. Parallel architectures**
- Contacts; cf. Ohmic contacts**
- Control systems; cf. Optical variables control**
- Copper materials/devices**
- freq.-doubled lasers for polymer high-speed UV micro-machining. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836
- He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
- laser-prod. plasma target materials for Xe²⁺ Auger laser pumping. *Dennis, T.*, +, *J-STQE Sep 95* 867-871
- Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
- vap. lasers, second harmonic and sum-freq. high av. power UV generation. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778
- vap. laser, UV SHG. *Withford, M.J.*, +, *J-STQE Sep 95* 779-783
- Corona**
- XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824

+ Check author entry for coauthors

† Check author entry for subsequent corrections/comments

Correlators; cf. Optical correlators
Corrugated waveguides; cf. Distributed feedback lasers
Couplers; cf. Laser couplers
Crosstalk; cf. Optical crosstalk
Current
 AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95 649-653*
 GaAsP-InGaAsP long wavelength strained QW lasers, orient. depend. of opt. props. *Niwa, A.*, +, *J-STQE Jun 95 211-217*
 GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95 293-300*
 GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T.*, +, *J-STQE Jun 95 697-706*
 InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang*, +, *J-STQE Jun 95 749-756*
 InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95 667-673*
 InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95 638-648*
 MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D.*, +, *J-STQE Jun 95 275-284*
 strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang*, +, *J-STQE Jun 95 218-229*

CVD

C, diamond-like films, excimer laser deposition using frozen acetylene. *Hanabusa, M.*, +, *J-STQE Sep 95 848-851*

CW lasers

AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95 728-733*
 AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95 723-727*
 antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95 129-137*
 GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95 173-182*
 InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95 165-172*
 InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95 110-116*
 InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95 203-210*
 Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95 859-866*
 Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95 784-791*
 rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95 427-432*
 semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95 150-164*
 semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95 505-515*
 ZnMgSse blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95 741-748*

D

Dielectric waveguides; cf. Optical waveguides

Diffusion processes

eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D.*, +, *J-STQE Dec 95 1037-1046*
 GaAs-AlGaAs MQW GRINSCH laser temp. sensitivity. *Dion, M.*, +, *J-STQE Jun 95 230-233*
 InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95 234-243*

Diode lasers; cf. Semiconductor lasers

Displays; cf. Flat panel displays

Distortion; cf. Laser beam distortion

Distributed Bragg reflector lasers

AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95 606-615*
 AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95 601-605*
 DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95 363-370*
 InGaAs-GaAs 0.48- μ m circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95 382-386*
 InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95 667-673*
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95 401-407*
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95 396-400*

+ Check author entry for coauthors

InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95 654-660*
 short-cavity lasers, electrooptic tuning, wide-band AM. *Tessler, N.*, +, *J-STQE Jun 95 490-493*
Distributed feedback lasers
 1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu*, +, *J-STQE Jun 95 375-381*
 chirped gratings, bent waveguides. *Hillmer, H.*, +, *J-STQE Jun 95 356-362*
 complex-coupled $\lambda/4$ -shifted lasers, flat FM response. *Okai, M.*, +, *J-STQE Jun 95 461-465*
 DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95 363-370*
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95 461-465*
 DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95 346-355*
 direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95 433-441*
 gain coupled lasers, current-induced gain gratings. *Kazmierski, C.*, +, *J-STQE Jun 95 371-374*
 high-power single-mode operation, S-bent waveguide. *Salzman, J.*, +, *J-STQE Jun 95 346-355*
 InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95 341-345*
 InGaAsP-InP MQW-DFB LD, 1.5 μ m FM response. *Jong-In Shim*, +, *J-STQE Jun 95 516-522*
 MQW DFB laser, self-pulsating 1.55- μ m, 12-64 GHz continuous freq. tuning. *Sartorius, B.*, +, *J-STQE Jun 95 535-538*
 rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95 427-432*
 semicond. lasers, femtosecond pulse generation, soliton-effect compression tech. *Ahmed, K.A.*, +, *J-STQE Jun 95 592-600*
 semicond. lasers with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95 583-591*
 three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95 416-426*
Doping; cf. Semiconductor device doping

E**Electric discharge pumping**

He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95 805-810*
 He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95 805-810*
 Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95 805-810*
 Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95 886-890*

Electric field effects; cf. Electrooptic materials/devices

Electric variables; cf. Current

Electroabsorption; cf. Electrooptic materials/devices; Electrooptic measurements

Electrodes

three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95 416-426*

Electroluminescent materials/devices

GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95 285-292*
 light-emitting porous Si materials sci., props., and device appls. *Faucher, P.M.*, +, *J-STQE Dec 95 1126-1139*

Electroluminescent materials/devices; cf. Light-emitting diodes

Electromagnetic coupling; cf. Optical coupling

Electromagnetic measurements; cf. Optical measurements

Electromagnetic propagation in absorbing media; cf. Optical propagation in absorbing media

Electromagnetic reflection; cf. Optical reflection

Electromagnetic refraction; cf. Optical refraction

Electron beam lithography

InGaAs-GaAs 0.48- μ m circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95 382-386*
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95 401-407*

Electron beam pumping

Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95 924-930*
 (HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95 877-885*
 (KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95 877-885*

† Check author entry for subsequent corrections/comments

- Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
- Electron spectroscopy**
CdTe-doped PTFE thin films, laser deposition. *Inoue, S.*, +, *J-STQE Sep 95* 908-915
- Electrooptic materials/devices**
InGaAsP/InP heterostructs., inhomog. exciton broadening and mean free path. *Jaeger, A.*, +, *J-STQE Dec 95* 1113-1118
semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
- Electrooptic materials/devices; cf. Electrooptic modulation; Kerr effect**
- Electrooptic measurements**
eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D.*, +, *J-STQE Dec 95* 1037-1046
wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H.*, +, *J-STQE Dec 95* 1002-1010
- Electrooptic modulation**
DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N.*, +, *J-STQE Jun 95* 490-493
InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 416-426
three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95* 723-727
wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H.*, +, *J-STQE Dec 95* 1002-1010
- Electrostatic analysis**
InP-based 1.3- μm QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95* 264-274
- Electrostatic processes; cf. Electrostatic analysis; Space charge**
- Energy storage**
Yb:Sr₃(PO₄)₃F 1.047- μm energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95* 67-77
- Epitaxial growth**
AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95* 102-109
AlGaN_{0.1}P fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
AlGaN_{0.1}P index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95* 723-727
AlGaN_{0.1}P vis. laser, H effect, high temp. operation. *Won-Jin Choi, +*, *J-STQE Jun 95* 717-722
AlGaN_{0.1}P vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wavelength. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628
GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C.*, +, *J-STQE Dec 95* 1119-1125
GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292
Ga(In)As(P)-GaInAsP-GaN_{0.1}P quantum well laser, strain influence on lasing perform. *Guodong Zhang, J-STQE Jun 95* 183-188
GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182
InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang, +*, *J-STQE Jun 95* 749-756
InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95* 382-386
InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao, +*, *J-STQE Jun 95* 196-202
InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
InGaAsP-InP MQW-DFB LD, 1.5 μm FM response. *Jong-In Shim, +*, *J-STQE Jun 95* 516-522
InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
pass. antiguided VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95* 629-637
rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
reson.-tunneling diode growth, opt. diagnostic monitoring. *Celii, F.G.*, +, *J-STQE Dec 95* 1064-1072
semicond. alloy comp. determ. during epitaxy, opt. methods. *Aspnes, D.E.*, *J-STQE Dec 95* 1054-1063
- Equivalent circuits**
quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N.*, +, *J-STQE Jun 95* 331-340
- Erbium materials/devices**
Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95* 14-21
- Etching**
1.3- μm strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu, +*, *J-STQE Jun 95* 375-381
InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
n-GaAs, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
n-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
- Excimer lasers**
193-nm lithog. technol. *Rothschild, M.*, +, *J-STQE Sep 95* 916-923
Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
Ar²⁺F⁻ ionic excimers, VUV spectra. *Chi Zhou, +*, *J-STQE Sep 95* 872-876
C, diamond-like films, excimer laser deposition using frozen acetylene. *Hanabusa, M.*, +, *J-STQE Sep 95* 848-851
(HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
(KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
Kr²⁺F⁻ ionic excimers, VUV spectra. *Chi Zhou, +*, *J-STQE Sep 95* 872-876
lithog. syst. throughput, laser-damage impact. *Harned, N.*, +, *J-STQE Sep 95* 837-840
N₂ capillary laser, 337.1 nm, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
- Excitation of lasers; cf. Laser excitation**

F

- Fabrication; cf. Integrated circuit fabrication; Optical device fabrication; Semiconductor device fabrication**
- Fabry-Perot resonators**
GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wavelength. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628
Ga(In)As(P)-GaInAsP-GaN_{0.1}P quantum well laser, strain influence on lasing perform. *Guodong Zhang, J-STQE Jun 95* 183-188
LD, self-seeded Fabry-Perot, time jitter/dyn. *Schell, M.*, +, *J-STQE Jun 95* 528-534
semicond. lasers, gain-switched operation, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95* 569-576
SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
- Faraday effect**
digital mag. heterostructs., spin dyns., time resolved Faraday rot. spectrosc. *Crooker, S.A.*, +, *J-STQE Dec 95* 1082-1092
- Feedback lasers**
DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N.*, +, *J-STQE Jun 95* 490-493
DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95* 363-370
DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
DFB laser, current-induced gain gratings. *Kazmiercki, C.*, +, *J-STQE Jun 95* 371-374
DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
InGaAsP-InP MQW-DFB LD, 1.5 μm FM response. *Jong-In Shim, +*, *J-STQE Jun 95* 516-522
InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95* 150-164
semicond. lasers, external opt. feedback phenom. *Petermann, K.*, *J-STQE Jun 95* 480-489
semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95* 505-515

Feedback lasers; cf. Distributed feedback lasers
Films; cf. Optical films; Semiconductor films
Filters; cf. Spatial filters
Flat panel displays
 thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95* 993-1001
Fluorescent materials/devices
 (HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
 (KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
 Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
 rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
FM; cf. Frequency modulation
FM pulse compression; cf. Chirp modulation
Focusing; cf. Laser beam focusing; Lenses
Forecasting; cf. Technology forecasting
Fourier spectroscopy
 GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C.*, +, *J-STQE Dec 95* 1119-1125
Frequency conversion; cf. Optical frequency conversion
Frequency division multiplexing; cf. Wavelength division multiplexing
Frequency domain analysis
 monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551
Frequency modulation
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95* 461-465
 InGaAsP-InP MQW-DFB LD, 1.5 μm FM response. *Jong-In Shim*, +, *J-STQE Jun 95* 516-522
 three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95* 416-426
Frequency stability; cf. Laser stability

G

Gallium materials/devices
 AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95* 606-615
 AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M.*, +, *J-STQE Jun 95* 473-479
 AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95* 102-109
 AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582
 AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95* 601-605
 AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
 AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95* 723-727
 AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95* 649-653
 AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi*, +, *J-STQE Jun 95* 717-722
 AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
 GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T.*, +, *J-STQE Jun 95* 562-568
 GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wavelength. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628
 GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95* 681-696
 GaAs-AlGaAs MQW GRINSLCH laser temp. sensitivity. *Dion, M.*, +, *J-STQE Jun 95* 230-233
 GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V.*, +, *J-STQE Jun 95* 552-561
 GaAsP-InGaAsP long wavelength strained QW lasers, orient. depend. of opt. props. *Niwa, A.*, +, *J-STQE Jun 95* 211-217
 GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
 GalnAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292
 Ga(In)As(P)-GalnAsP-GalnP quantum well laser, strain influence on lasing perform. *Guodong Zhang*, *J-STQE Jun 95* 183-188
 GalnAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95* 293-300

+ Check author entry for coauthors

GalnP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T.*, +, *J-STQE Jun 95* 697-706
 GalnP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182
 GalnP quantum well laser, threshold current strain depend. *Blood, P.*, +, *J-STQE Jun 95* 707-711
 InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95* 712-716
 InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95* 382-386
 InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao*, +, *J-STQE Jun 95* 196-202
 InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95* 165-172
 InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
 InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sum, D.*, +, *J-STQE Jun 95* 674-680
 InGaAs-GaAs VCSEL, polaris. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673
 InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
 InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95* 234-243
 InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95* 308-315
 InGaAs-InGaP 0.98- μm strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M.*, +, *J-STQE Jun 95* 244-249
 InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M.*, +, *J-STQE Jun 95* 189-194
 InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim*, +, *J-STQE Jun 95* 408-415
 InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395
 InGaAsP-InP MQW-DFB LD, 1.5 μm FM response. *Jong-In Shim*, +, *J-STQE Jun 95* 516-522
 InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95* 203-210
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95* 401-407
 InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95* 638-648
 InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
 InGaAs subms tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
 InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
 InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95* 654-660
 Ne-like lasing, prepulse effect. *Fill, E.E.*, +, *J-STQE Sep 95* 958-961
 n-GaAs, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
Gas discharge devices; cf. Glow discharge devices
Gas discharges; cf. Corona; Ionization; Sparks
Gas lasers
 Cu freq.-doubled lasers for polymer high-speed UV micro-machining. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836
 Cu vap. laser, second-harmonic and sum-freq. high av. power UV generation. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778
 Cu vap. laser, UV SHG. *Withford, M.J.*, +, *J-STQE Sep 95* 779-783
 N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
Gas lasers; cf. Excimer lasers; Ion lasers
Gaussian beams
 Hg vap., intense VUV coherent light generation, nonlin. effects. *Museum, L.*, +, *J-STQE Sep 95* 900-907
Geometrical optics
 corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95* 1156
 Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95* 949-957
Germanium materials/devices
 corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95* 1156
 Ne-like Ge collisionally-pumped laser, prepulse effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95* 949-957

† Check author entry for subsequent corrections/comments

Glass materials/devices; cf. Neodymium:glass lasers**Glow discharge devices**

- He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810

Gold materials/devices

- He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 laser-prod. plasma target materials for Xe²⁺ Auger laser pumping. *Dennis, T.*, +, *J-STQE Sep 95* 867-871

Gratings

- DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95* 363-370
 DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
 DFB laser, current-induced gain gratings. *Kazmiercki, C.*, +, *J-STQE Jun 95* 371-374
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95* 461-465
 DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
 DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
 InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95* 382-386
 InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95* 401-407
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
 semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95* 505-515

Gratings; cf. Holographic gratings**H****Harmonic generation; cf. Optical frequency conversion****Helium materials/devices**

- (HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
 He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810

Heterojunction bipolar transistors

- high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H.*, +, *J-STQE Dec 95* 1030-1036
 opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95* 1011-1016

Heterojunctions; cf. Semiconductor heterojunctions**High-temperature factors; cf. High-temperature techniques****High-temperature techniques**

- AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95* 102-109

Holographic gratings

- InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 n-GaAs, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 n-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847

Holographic optical components; cf. Holographic gratings**I****Imaging/mapping; cf. Infrared imaging/mapping; Microscopy; Optical imaging/mapping****Indium materials/devices**

- AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
 AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95* 723-727
 AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95* 649-653
 AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi, +*, *J-STQE Jun 95* 717-722

+ Check author entry for coauthors

- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740

- GaAsP-InGaAsP long wavelength strained QW lasers, orient. depend. of opt. props. *Niwa, A.*, +, *J-STQE Jun 95* 211-217

- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292

- Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on las-ing perform. *Guodong Zhang, J-STQE Jun 95* 183-188

- GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95* 293-300

- GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T.*, +, *J-STQE Jun 95* 697-706

- GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182

- GaInP quantum well laser, threshold current strain depend. *Blood, P.*, +, *J-STQE Jun 95* 707-711

- InAs-InAsSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang, +*, *J-STQE Jun 95* 749-756

- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95* 712-716

- InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95* 382-386

- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao, +*, *J-STQE Jun 95* 196-202

- InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou, +*, *J-STQE Jun 95* 165-172

- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623

- InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95* 674-680

- InGaAs-GaAs VCSEL, polaris. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673

- InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345

- InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95* 234-243

- InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95* 308-315

- InGaAs-InGaP 0.98- μm strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M.*, +, *J-STQE Jun 95* 244-249

- InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M.*, +, *J-STQE Jun 95* 189-194

- InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847

- InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim, +*, *J-STQE Jun 95* 408-415

- InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395

- InGaAsP/InP heterostructs., inhomog. exciton broadening and mean free path. *Jaeger, A.*, +, *J-STQE Dec 95* 1113-1118

- InGaAsP-InP MQW-DFB LD, 1.5 μm FM response. *Jong-In Shim, +*, *J-STQE Jun 95* 516-522

- InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95* 203-210

- InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95* 401-407

- InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95* 638-648

- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450

- InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400

- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666

- InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95* 654-660

- InP-based 1.3- μm QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95* 264-274

- n-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847

Industrial control; cf. Process control**Infrared imaging/mapping**

- InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95* 110-116

Infrared lasers; cf. Lasers**Infrared spectroscopy**

- GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C.*, +, *J-STQE Dec 95* 1119-1125

† Check author entry for subsequent corrections/comments

Injection lasers; cf. Semiconductor lasers
Innovation; cf. Technological innovation
Integrated circuit fabrication
 193-nm lithog. technol. *Rothschild, M.*, +, *J-STQE Sep 95* 916-923
Integrated circuit fabrication; cf. Resistors
Integrated circuits; cf. Integrated optoelectronics
Integrated optics
 AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
 antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95* 129-137
 InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95* 165-172
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527
Integrated optoelectronics
 InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95* 203-210
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
 quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N.*, +, *J-STQE Jun 95* 331-340
 semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
Interchannel interference; cf. Optical crosstalk
Interconnections; cf. Optical interconnections
Interferometry; cf. Optical interferometry
Invention; cf. Technological innovation
Ion implantation; cf. Semiconductor device ion implantation
Ionization
 Li⁺ opt. field-induced ionization X-ray laser, preformed plasma. *Midorikawa, K.*, +, *J-STQE Sep 95* 931-940
 XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
Ionization; cf. Photoionization
Ion lasers
 Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95* 945-948
 corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95* 1156
 Ga, Ne-like lasing, prepulse effect. *Fill, E.E.*, +, *J-STQE Sep 95* 958-961
 Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95* 949-957
 He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 Li⁺ opt. field-induced ionization X-ray laser, preformed plasma. *Midorikawa, K.*, +, *J-STQE Sep 95* 931-940
 Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 Ta laser double-pass, CrB₂-C multilayer mirror damage, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
 Xe²⁺ Auger laser, pumping by laser-prod. target materials. *Dennis, T.*, +, *J-STQE Sep 95* 867-871

J

Jitter; cf. Timing jitter
Junction lasers; cf. Semiconductor lasers
Junctions; cf. Semiconductor-insulator interfaces

K

Kerr effect
 Hg vap., intense VUV coherent light generation, nonlin. effects. *Museur, L.*, +, *J-STQE Sep 95* 900-907
Krypton materials/devices
 (KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885
 Kr²⁺F⁺ ionic excimers, VUV spectra. *Chi Zhou*, +, *J-STQE Sep 95* 872-876

+ Check author entry for coauthors

L

Lamps; cf. Lighting
Lanthanum materials/devices
 ZBLAN:Nd fiber laser in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
Laser absorbers
 GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T.*, +, *J-STQE Jun 95* 562-568
 GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V.*, +, *J-STQE Jun 95* 552-561
 InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395
 Tm:YAlO₃ 1.94- μ m laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81
Laser accessories
 AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
 CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
 DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95* 363-370
 DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
 DFB laser, current-induced gain gratings. *Kazmierski, C.*, +, *J-STQE Jun 95* 371-374
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95* 461-465
 DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
 GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95* 293-300
 InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95* 165-172
 InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673
 InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
 InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
 N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
 XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
Laser accessories; cf. Laser absorbers; Laser couplers; Laser resonators
Laser amplifiers
 antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95* 129-137
 Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95* 945-948
 Cu vap. laser, second-harmonic and sum-freq. high av. power UV generation. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527
 Yb:Sr₃(PO₄)₃F 1.047- μ m energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95* 67-77
Laser amplifiers; cf. Semiconductor optical amplifiers
Laser applications
 InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 lithog. syst. throughput, laser-damage impact. *Harned, N.*, +, *J-STQE Sep 95* 837-840
 n-GaAs, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 n-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95* 841-847
 polymers, high-speed UV micro-machining, freq.-doubled Cu vap. lasers. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836
Laser applications; cf. Laser biomedical applications; Laser materials-processing applications
Laser arrays; cf. Semiconductor laser arrays
Laser beam distortion
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
Laser beam effects; cf. Laser applications; Laser radiation effects
Laser beam focusing
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
Laser beams
 AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582

† Check author entry for subsequent corrections/comments

- AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95* 601-605
- AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
- AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95* 723-727
- AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95* 649-653
- AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi*, +, *J-STQE Jun 95* 717-722
- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
- Cu vap. laser, UV SHG. *Withford, M.J.*, +, *J-STQE Sep 95* 779-783
- DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
- DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
- DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
- DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
- Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95* 569-576
- GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on lasing perform. *Guodong Zhang*, *J-STQE Jun 95* 183-188
- GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95* 293-300
- GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T.*, +, *J-STQE Jun 95* 697-706
- GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182
- GaInP quantum well laser, threshold current strain depend. *Blood, P.*, +, *J-STQE Jun 95* 707-711
- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95* 712-716
- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao*, +, *J-STQE Jun 95* 196-202
- InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95* 165-172
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
- InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95* 674-680
- InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95* 308-315
- InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M.*, +, *J-STQE Jun 95* 189-194
- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95* 654-660
- N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
- semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95* 150-164
- XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
- ZnMgSSe blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95* 741-748
- Laser biomedical applications**
Tm:YAlO₃ 1.94- μ m laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81
- Laser cavity resonators; cf. Laser resonators**
- Laser components; cf. Laser accessories**
- Laser couplers**
DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
- InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
- Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95* 150-164
- semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95* 757-761
- Laser diodes; cf. Semiconductor lasers**
- Laser excitation**
Yb³⁺:SiO₂ fiber lasers, sources 1, 1.2 μ m. *Pask, H.M.*, +, *J-STQE Apr 95* 2-13
- Laser excitation; cf. Electric discharge pumping; Electron beam pumping; Optical pumping**
- Laser materials-processing applications**
C, diamond-like films, excimer laser deposition using frozen acetylene. *Hanabusa, M.*, +, *J-STQE Sep 95* 848-851
- CdTe-doped PTFE thin films, laser deposition. *Inoue, S.*, +, *J-STQE Sep 95* 908-915
- Laser modes**
1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu*, +, *J-STQE Jun 95* 375-381
- AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95* 606-615
- AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M.*, +, *J-STQE Jun 95* 473-479
- AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95* 102-109
- AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
- AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95* 723-727
- AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi*, +, *J-STQE Jun 95* 717-722
- antiguidd diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95* 138-149
- antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95* 129-137
- DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
- DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
- Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95* 569-576
- GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
- InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395
- InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95* 638-648
- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- LD, self-seeded Fabry-Perot, time jitter/dyn. *Schell, M.*, +, *J-STQE Jun 95* 528-534
- Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
- pass. antiguidd VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95* 629-637
- quantum well high-speed lasers, carrier transport effects, time-domain model. *Nguyen, L.V.T.*, +, *J-STQE Jun 95* 494-504
- semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95* 150-164
- semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W.*, +, *J-STQE Jun 95* 117-128
- semicond. laser, opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95* 466-472
- semicond. lasers, external opt. feedback phenom. *Petermann, K.*, *J-STQE Jun 95* 480-489
- semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95* 757-761
- Laser modes; cf. Mode locked lasers**
- Laser noise**
Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95* 569-576
- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
- semicond. laser, opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95* 466-472
- semicond. lasers, external opt. feedback phenom. *Petermann, K.*, *J-STQE Jun 95* 480-489
- semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95* 505-515
- Laser pulses; cf. Optical pulses; Pulsed lasers**
- Laser radiation effects**
CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
- lithog. syst. throughput, laser-damage impact. *Harned, N.*, +, *J-STQE Sep 95* 837-840

Laser reliability

- AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95 102-109*
 Ce^{3+} activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95 792-804*
 InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95 712-716*
 ZnMgSSe blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95 741-748*

Laser resonators

- AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95 606-615*
 AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95 577-582*
 AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95 601-605*
 AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95 723-727*
 AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95 649-653*
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95 924-930*
 DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N.*, +, *J-STQE Jun 95 490-493*
 DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C.*, *J-STQE Jun 95 363-370*
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95 461-465*
 DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95 346-355*
 Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95 569-576*
 GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. *Eng, L.E.*, +, *J-STQE Jun 95 624-628*
 GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95 681-696*
 GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95 661-666*
 Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on lasing perform. *Guodong Zhang, J-STQE Jun 95 183-188*
 InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95 616-623*
 InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95 674-680*
 InGaAs-GaAs VCSEL, polaris. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95 667-673*
 InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95 387-395*
 InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95 203-210*
 InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95 638-648*
 InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95 442-450*
 InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95 661-666*
 InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95 654-660*
 LD, self-seeded Fabry-Perot, time jitter/dyn. *Schell, M.*, +, *J-STQE Jun 95 528-534*
 MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D.*, +, *J-STQE Jun 95 275-284*
 Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95 859-866*
 pass. antiguide VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95 629-637*
 semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W.*, +, *J-STQE Jun 95 117-128*
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalifin, V.B.*, +, *J-STQE Jun 95 523-527*
 semicond. lasers, external opt. feedback phenom. *Petermann, K.*, *J-STQE Jun 95 480-489*
 semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95 505-515*
 semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95 757-761*
 SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95 941-944*
 XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95 811-824*

Lasers

- short wavelength lasers and applications (special issue). *J-STQE Sep 95 765-975*

Lasers; cf. CW lasers; Distributed Bragg reflector lasers; Excimer lasers; Feedback lasers; Gas lasers; Laser amplifiers; Power lasers; Pulsed lasers; Ring lasers; Solid lasers; X-ray lasers

Laser stability

- AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R.*, +, *J-STQE Jun 95 723-727*
 AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95 734-740*
 antiguided diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95 138-149*
 DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95 356-362*
 Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95 14-21*
 InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95 674-680*
 InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95 638-648*
 semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95 150-164*
 semicond. laser, opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95 466-472*

Laser thermal factors

- 1.3 μm semicond. lasers, gain anal. in To determination. *Ackerman, D.A.*, +, *J-STQE Jun 95 250-263*
 1.3- μm strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Han Lu, +, J-STQE Jun 95 375-381*
 Cr⁴⁺-doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95 62-66*
 GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. *Eng, L.E.*, +, *J-STQE Jun 95 624-628*
 GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95 681-696*
 GaAs-AlGaAs MQW GRINSCH laser temp. sensitivity. *Dion, M.*, +, *J-STQE Jun 95 230-233*
 GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95 285-292*
 GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95 293-300*
 InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95 234-243*
 InGaAs-InGaP 0.98- μm strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M.*, +, *J-STQE Jun 95 244-249*
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95 401-407*
 InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95 638-648*
 InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95 654-660*
 InP-based 1.3- μm QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95 264-274*
 MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D.*, +, *J-STQE Jun 95 275-284*
 quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N.*, +, *J-STQE Jun 95 331-340*
 rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95 427-432*
 strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang, +, J-STQE Jun 95 218-229*

Laser tuning

- Ce^{3+} activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95 792-804*
 Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95 58-61*
 Cr⁴⁺-doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95 62-66*
 DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N.*, +, *J-STQE Jun 95 490-493*
 DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95 356-362*
 DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95 461-465*
 Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95 14-21*
 InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim, +, J-STQE Jun 95 408-415*
 InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95 387-395*
 InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95 401-407*
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg scct. *Delorme, F.*, +, *J-STQE Jun 95 396-400*

+ Check author entry for coauthors

† Check author entry for subsequent corrections/comments

- LiF:F₂ color center laser progress. *Mirov, S.B.*, +, *J-STQE Apr 95* 22-30
 MQW DFB laser, self-pulsating 1.55- μ m, 12-64 GHz continuous freq. tuning. *Sartorius, B.*, +, *J-STQE Jun 95* 535-538
 rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95* 427-432
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527
 SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
 three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95* 416-426
 Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57
 tunable solid-state lasers (special issue). *J-STQE Apr 95* 1-91
 ZnMgSse blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95* 741-748
- LEDs; cf. Light-emitting diodes**
- Lenses**
 InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou*, +, *J-STQE Jun 95* 165-172
- Light-emitting diodes**
 III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R.*, *J-STQE Dec 95* 987-992
 light-emitting porous Si materials sci., props., and device appls. *Fauchet, P.M.*, +, *J-STQE Dec 95* 1126-1139
- Lighting**
 Xe excimer lamp excitation by quasi-CW jet discharges. *Kawanaka, J.*, +, *J-STQE Sep 95* 852-858
- Light sources; cf. Lasers; Light-emitting diodes; Lighting**
- Linear algebra; cf. Matrices**
- Linear FM; cf. Chirp modulation**
- Lithium materials/devices**
 LiB₃O₅ cryst. opt. harmonic generation of Ti:sapphire laser wavelengths. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57
 LiCaAlF₆:Ce³⁺, tunable UV ultrafast lasers, direct pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
 LiF:F₂ color center laser progress. *Mirov, S.B.*, +, *J-STQE Apr 95* 22-30
 LiSrAlF₆:Cr laser, Q-switched, SHG. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61
 Li⁺ opt. field-induced ionization X-ray laser, preformed plasma. *Midorikawa, K.*, +, *J-STQE Sep 95* 931-940
 LuLiF₄:Ce³⁺, tunable UV ultrafast lasers, direct pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- Lithography; cf. Electron beam lithography; Photolithography; X-ray lithography**
- Losses; cf. Optical losses**
- Luminescent materials/devices; cf. Electroluminescent materials/devices; Fluorescent materials/devices; Photoluminescent materials/devices**
- Lutetium materials/devices**
 LuLiF₄:Ce³⁺, tunable UV ultrafast lasers, direct pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- M**
- Magnesium materials/devices**
 ZnMgSse blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95* 741-748
- Magnetic materials/devices**
 digital mag. heterostructs., spin dyns., time resolved Faraday rot. spectrosc. *Crooker, S.A.*, +, *J-STQE Dec 95* 1082-1092
- Magneto-optic materials/devices; cf. Faraday effect**
- Manufacturing testing**
 HBT opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95* 1011-1016
 high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H.*, +, *J-STQE Dec 95* 1030-1036
 large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95* 1017-1029
 LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R.*, *J-STQE Dec 95* 987-992
 optical diagnostics of semiconductors (special issue). *J-STQE Dec 95* 977-1155
 thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95* 993-1001
 wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E.*, +, *J-STQE Dec 95* 980-986
 wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H.*, +, *J-STQE Dec 95* 1002-1010
- Mass spectroscopy**
 AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi*, +, *J-STQE Jun 95* 717-722
- Materials processing; cf. Etching; Laser materials-processing applications**
- Materials testing; cf. Nondestructive testing**
- Mathematics; cf. Optimization methods**
- Matrices**
 strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang*, +, *J-STQE Jun 95* 218-229
- Measurement; cf. Semiconductor device measurements; Semiconductor materials measurements; Spectroscopy**
- Mechanical factors; cf. Semiconductor device mechanical factors; Strain**
- Mercury materials/devices**
 vap., intense VUV coherent light generation, nonlin. effects. *Museur, L.*, +, *J-STQE Sep 95* 900-907
- Microscopy**
 InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95* 110-116
 semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B.*, +, *J-STQE Dec 95* 1073-1081
- Mirrors**
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
 CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
 GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A.*, +, *J-STQE Jun 95* 293-300
 InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
- Modeling; cf. Semiconductor device modeling**
- Mode locked lasers**
 AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582
 GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V.*, +, *J-STQE Jun 95* 552-561
 InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
 monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551
 MQW DFB laser, self-pulsating 1.55- μ m, 12-64 GHz continuous freq. tuning. *Sartorius, B.*, +, *J-STQE Jun 95* 535-538
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527
 semicond. laser, opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95* 466-472
 semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
- Modulation/demodulation; cf. Chirp modulation; Optical modulation/demodulation**
- Monitoring; cf. Process monitoring**
- Multiplexing; cf. Wavelength division multiplexing**
- N**
- Negative resistance devices; cf. Tunnel diodes**
- Neodymium:glass lasers**
 Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- Neodymium:YAG lasers**
 Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- Neon materials/devices**
 Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810
 Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
- Nitrogen materials/devices**
 laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
 N₂ capillary laser, 337.1 nm, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
- Noble gas materials/devices; cf. Argon materials/devices; Helium materials/devices; Krypton materials/devices; Neon materials/devices; Xenon materials/devices**
- Noise; cf. Laser noise**
- Nondestructive testing**
 eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biermacki, P.D.*, +, *J-STQE Dec 95* 1037-1046
 HBT opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95* 1011-1016
 large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95* 1017-1029
 LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R.*, *J-STQE Dec 95* 987-992

- wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E.*, +, *J-STQE Dec 95* 980-986
- wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H.*, +, *J-STQE Dec 95* 1002-1010
- Nonlinear optics**
- AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582
- antiguide diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95* 138-149
- semicond. quantum well laser, carrier transport, nonlin. gain coeffs. *Chin-Yi Tsai*, +, *J-STQE Jun 95* 316-330
- SHG, unamplified high-repetition-rate, ultrashort laser pulses at Si(001) interfaces. *Dadap, J.I.*, +, *J-STQE Dec 95* 1145-1155
- Xe, VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899
- Nonlinear optics; cf. Optical mixing; Optical saturation**
- O
- Ohmic contacts**
- eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D.*, +, *J-STQE Dec 95* 1037-1046
- Optical amplifiers; cf. Laser amplifiers; Optical fiber amplifiers; Optical pulse amplifiers; Semiconductor optical amplifiers**
- Optical beam focusing; cf. Laser beam focusing**
- Optical beams; cf. Laser beams**
- Optical communication; cf. Optical fiber communication; Wavelength division multiplexing**
- Optical communication equipment**
- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450
- rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95* 427-432
- Optical communication equipment; cf. Optical receivers**
- Optical components; cf. Lenses; Mirrors**
- Optical correlators**
- monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551
- Optical couplers; cf. Laser couplers; Optical fiber couplers; Optical strip waveguide couplers**
- Optical coupling**
- 1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu*, +, *J-STQE Jun 95* 375-381
- InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
- semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E.*, +, *J-STQE Jun 95* 150-164
- strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang*, +, *J-STQE Jun 95* 218-229
- Optical coupling; cf. Optical fiber coupling**
- Optical crosstalk**
- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
- GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95* 681-696
- Optical device fabrication**
- AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M.*, +, *J-STQE Jun 95* 473-479
- AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M.*, +, *J-STQE Jun 95* 728-733
- AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi*, +, *J-STQE Jun 95* 717-722
- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A.*, +, *J-STQE Jun 95* 734-740
- DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95* 461-465
- GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628
- GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M.*, +, *J-STQE Jun 95* 285-292
- Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on las-ing perform. *Guodong Zhang*, *J-STQE Jun 95* 183-188
- GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95* 173-182
- InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang*, +, *J-STQE Jun 95* 749-756
- InGaAs-GaAs 0.48- μ m circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95* 382-386
- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao*, +, *J-STQE Jun 95* 196-202
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
- InGaAsP-InP MQW-DFB LD, 1.5 μ m FM response. *Jong-In Shim*, +, *J-STQE Jun 95* 516-522
- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666
- Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- pass. antiguide VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95* 629-637
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
- semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95* 757-761
- Optical distortion; cf. Laser beam distortion; Optical crosstalk**
- Optical feedback**
- semicond. laser, opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95* 466-472
- Optical fiber amplifiers**
- Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95* 14-21
- Optical fiber communication**
- direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95* 433-441
- Optical fiber couplers**
- semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95* 757-761
- Optical fiber coupling**
- DFB semicond. laser, femtosecond pulse generation, soliton effect com-pression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
- Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95* 14-21
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623
- Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- Optical fiber dispersion**
- direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95* 433-441
- Optical fiber lasers**
- Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- Yb³⁺:SiO₂ fiber lasers, sources 1, 1.2 μ m. *Pask, H.M.*, +, *J-STQE Apr 95* 2-13
- Optical fiber lasers; cf. Optical fiber amplifiers**
- Optical fiber polarization**
- Er-doped widely tunable polariz.-stable fiber lasers. *Cooper, D.G.*, +, *J-STQE Apr 95* 14-21
- Optical films**
- CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakitreva, L.L.*, +, *J-STQE Sep 95* 962-969
- InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95* 110-116
- InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95* 203-210
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
- Optical frequency conversion**
- Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61
- Cu freq.-doubled lasers for polymer high-speed UV micro-machining. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836
- Cu vap. laser, second-harmonic and sum-freq. high av. power UV genera-tion. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778
- Cu vap. laser, UV SHG. *Withford, M.J.*, +, *J-STQE Sep 95* 779-783
- Hg vap., intense VUV coherent light generation, nonlin. effects. *Museum, L.*, +, *J-STQE Sep 95* 900-907
- LiF:F₂ color center laser progress. *Mirov, S.B.*, +, *J-STQE Apr 95* 22-30
- Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
- semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
- SHG, unamplified high-repetition-rate, ultrashort laser pulses at Si(001) interfaces. *Dadap, J.I.*, +, *J-STQE Dec 95* 1145-1155
- β -BaB₂O₄, intracavity freq. doubled CW Nd:YAG laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866
- Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57

- Optical frequency conversion; cf. Optical mixing**
- Optical imaging/mapping**
large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95* 1017-1029
- Optical interconnections**
InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95* 203-210
- Optical interferometry**
AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49
Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95* 569-576
large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95* 1017-1029
- Optical links; cf. Optical interconnections**
- Optical losses**
AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M.*, +, *J-STQE Jun 95* 473-479
antiguided diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95* 138-149
InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95* 341-345
InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim*, +, *J-STQE Jun 95* 408-415
InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395
pass. antiguide VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95* 629-637
rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
Tm:YAlO₃ 1.94- μ m laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81
- Optical materials/devices**
193-nm lithog. technol. *Rothschild, M.*, +, *J-STQE Sep 95* 916-923
AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49
Cr⁴⁺-doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95* 62-66
KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95* 31-43
- Optical materials/devices; cf. Electrooptic materials/devices; Optical correlators; Optical oscillators; Optical receivers; Optical waveguides**
- Optical measurements**
HBT opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95* 1011-1016
LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R.*, *J-STQE Dec 95* 987-992
optical diagnostics of semiconductors (special issue). *J-STQE Dec 95* 977-1155
real-time opt. thermometry during semicond. proc. *Herman, I.P.*, *J-STQE Dec 95* 1047-1053
reson.-tunneling diode growth, opt. diagnostic monitoring. *Celii, F.G.*, +, *J-STQE Dec 95* 1064-1072
semicond. alloy comp. determ. during epitaxy, opt. methods. *Aspnes, D.E.*, *J-STQE Dec 95* 1054-1063
thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95* 993-1001
wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E.*, +, *J-STQE Dec 95* 980-986
- Optical measurements; cf. Electrooptic measurements; Microscopy; Optical interferometry; Optical spectroscopy**
- Optical mixing**
Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61
Hg vap., intense VUV coherent light generation, nonlin. effects. *Museur, L.*, +, *J-STQE Sep 95* 900-907
semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
- Optical modulation/demodulation**
1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu*, +, *J-STQE Jun 95* 375-381
DFB laser, current-induced gain gratings. *Kazmierski, C.*, +, *J-STQE Jun 95* 371-374
DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95* 461-465
DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95* 433-441
InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95* 234-243
InGaAsP-InP MQW-DFB LD, 1.5 μ m FM response. *Jong-In Shim*, +, *J-STQE Jun 95* 516-522
- semicond. laser, mode-locked, synchronization with external pulse stream. *Khafin, V.B.*, +, *J-STQE Jun 95* 523-527
semicond. lasers, grating-terminated external cavity, small-sig. IM response. *Ahmed, Z.*, +, *J-STQE Jun 95* 505-515
- Optical modulation/demodulation; cf. Electrooptic modulation**
- Optical noise; cf. Laser noise**
- Optical oscillators**
antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95* 129-137
Cu vap. laser, second-harmonic and sum-freq. high av. power UV generation. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778
rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
- Optical oscillators; cf. Lasers; Optical parametric oscillators**
- Optical parametric oscillators**
AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49
KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95* 31-43
- Optical planar waveguide components**
large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95* 1017-1029
rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
- Optical polarization**
InGaAs-GaAs VCSEL, polaris. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673
Tm:YAlO₃ 1.94- μ m laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81
Yb:Sr₃(PO₄)₃F 1.047- μ m energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95* 67-77
- Optical polarization; cf. Optical fiber polarization**
- Optical propagation; cf. Optical propagation in absorbing media; Optical waveguides**
- Optical propagation in absorbing media**
InGaAsP/InP heterostructs., inhomog. exciton broadening and mean free path. *Jaeger, A.*, +, *J-STQE Dec 95* 1113-1118
semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95* 451-460
- Optical propagation in absorbing media; cf. Laser absorbers**
- Optical propagation in dispersive media; cf. Optical fiber dispersion; Optical solitons**
- Optical propagation in nonlinear media; cf. Optical frequency conversion; Optical solitons**
- Optical pulse amplifiers**
Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
- Optical pulse compression**
DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551
N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
Xe, VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899
- Optical pulse generation**
AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582
Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
- Optical pulses**
Xe excimer lamp excitation by quasi-CW jet discharges. *Kawanaka, J.*, +, *J-STQE Sep 95* 852-858
- Optical pulses; cf. Optical solitons**
- Optical pulse shaping**
DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600
DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591
- Optical pumping**
AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49
Ar²⁺ ionic excimers, VUV spectra. *Chi Zhou*, +, *J-STQE Sep 95* 872-876
Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804
Cr⁴⁺-doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95* 62-66

- DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C., J-STQE Jun 95 363-370*
- InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang, +, J-STQE Jun 95 749-756*
- InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polariz. control. *Sun, D., +, J-STQE Jun 95 674-680*
- Kr²⁺F⁻ ionic excimers, VUV spectra. *Chi Zhou, +, J-STQE Sep 95 872-876*
- Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M., +, J-STQE Sep 95 859-866*
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A., +, J-STQE Apr 95 82-91*
- Xe²⁺ Auger laser, pumping by laser-prod. target materials. *Dennis, T., +, J-STQE Sep 95 867-871*
- Yb:Sr₃(PO₄)₃F 1.047- μ m energy storage opt. amp. *Marshall, C.D., +, J-STQE Apr 95 67-77*
- Yb³⁺:SiO₂ fiber lasers, sources 1, 1.2 μ m. *Pask, H.M., +, J-STQE Apr 95 2-13*
- Optical radiation effects; cf. Laser radiation effects; Photoionization**
- Optical receivers**
direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C., +, J-STQE Jun 95 433-441*
- Optical reflection**
CrB₂-C multilayer mirror damage, Ta laser double-pass, computer simul. *Balakireva, L.L., +, J-STQE Sep 95 962-969*
- GaNAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A., +, J-STQE Jun 95 293-300*
- InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T., +, J-STQE Jun 95 667-673*
- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U., +, J-STQE Jun 95 442-450*
- MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D., +, J-STQE Jun 95 275-284*
- semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W., +, J-STQE Jun 95 117-128*
- Optical reflection; cf. Mirrors**
- Optical refraction**
AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M., +, J-STQE Jun 95 473-479*
- DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N., +, J-STQE Jun 95 490-493*
- Ga, Ne-like lasing, prepulse effect. *Fill, E.E., +, J-STQE Sep 95 958-961*
- InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim, +, J-STQE Jun 95 408-415*
- InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C., +, J-STQE Jun 95 387-395*
- Li⁺ opt. field-induced ionization X-ray laser, preformed plasma. *Midorikawa, K., +, J-STQE Sep 95 931-940*
- pass. antiguide VCSEL, single-mode operation. *Wu, Y.A., +, J-STQE Jun 95 629-637*
- Optical resonance**
direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C., +, J-STQE Jun 95 433-441*
- Optical resonators; cf. Fabry-Perot resonators; Laser resonators**
- Optical saturation**
AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M., +, J-STQE Jun 95 473-479*
- Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J., +, J-STQE Sep 95 945-948*
- semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B., +, J-STQE Jun 95 523-527*
- Yb:Sr₃(PO₄)₃F 1.047- μ m energy storage opt. amp. *Marshall, C.D., +, J-STQE Apr 95 67-77*
- Optical signal processing; cf. Optical correlators**
- Optical solitons**
DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A., +, J-STQE Jun 95 592-600*
- Optical spectroscopy**
ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S., +, J-STQE Dec 95 1100-1107*
- digital mag. heterostructs., spin dyns., time resolved Faraday rot. spectrosc. *Crooker, S.A., +, J-STQE Dec 95 1082-1092*
- GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C., +, J-STQE Dec 95 1119-1125*
- HBT opt. charactn. *Smith, P.B., +, J-STQE Dec 95 1011-1016*
- high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H., +, J-STQE Dec 95 1030-1036*
- semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B., +, J-STQE Dec 95 1073-1081*
- semiconds., double AC photoreflectance spectrosc. *Ghosh, S., +, J-STQE Dec 95 1108-1112*
- spectrosc. study of red light emission in porous Si. *Prokes, S.M., J-STQE Dec 95 1140-1144*
- Optical spectroscopy; cf. Raman spectroscopy**
- Optical strip waveguide components; cf. Optical strip waveguide couplers**
- Optical strip waveguide couplers**
semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F., +, J-STQE Jun 95 757-761*
- Optical transient propagation; cf. Optical solitons**
- Optical variables control**
semicond. laser arrays, feedback stabilization, complex coupling coeffs. *Hill, D.E., +, J-STQE Jun 95 150-164*
- Optical waveguides**
GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V., +, J-STQE Jun 95 552-561*
- InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou, +, J-STQE Jun 95 165-172*
- Optics; cf. Geometrical optics; Integrated optics; Nonlinear optics; Ultrafast optics**
- Optimization methods**
MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D., +, J-STQE Jun 95 275-284*
- Optoelectronic devices**
DFB laser, current-induced gain gratings. *Kazmierski, C., +, J-STQE Jun 95 371-374*
- large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C., +, J-STQE Dec 95 1017-1029*
- Optoelectronic devices; cf. Integrated optoelectronics; Lasers; Light-emitting diodes**
- Oscillator noise; cf. Laser noise**
- Oscillators; cf. Lasers; Optical oscillators; Tunable oscillators**
- Oscillator stability; cf. Laser stability**

P

Parallel architectures

InGaAsP-InP MQW monolithic laser array. *Uomi, K., +, J-STQE Jun 95 203-210*

Parametric oscillators; cf. Optical parametric oscillators**Particle collisions**

corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B., +, J-STQE Dec 95 1156*

Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B., +, J-STQE Sep 95 949-957*

(HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H., +, J-STQE Sep 95 877-885*

(KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H., +, J-STQE Sep 95 877-885*

Periodic structures; cf. Arrays; Gratings**Photoionization**

Xe²⁺ Auger laser, pumping by laser-prod. target materials. *Dennis, T., +, J-STQE Sep 95 867-871*

Photolithography

193-nm lithog. technol. *Rothschild, M., +, J-STQE Sep 95 916-923*

EUV lithog. at 13 nm, current status. *Stulen, R.H., J-STQE Sep 95 970-975*

Laser-damage impact on lithog. syst. throughput. *Harned, N., +, J-STQE Sep 95 837-840*

Photoluminescent materials/devices

AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M., +, J-STQE Jun 95 728-733*

AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi, +, J-STQE Jun 95 717-722*

GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C., +, J-STQE Dec 95 1119-1125*

GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T., +, J-STQE Jun 95 697-706*

GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J., +, J-STQE Jun 95 173-182*

InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M., +, J-STQE Sep 95 841-847*

LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R., J-STQE Dec 95 987-992*

spectrosc. study of red light emission in porous Si. *Prokes, S.M., J-STQE Dec 95 1140-1144*

wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E., +, J-STQE Dec 95 980-986*

Photon beams; cf. Laser beams**Photonic integrated circuits; cf. Integrated optics****Photonics; cf. Optical materials/devices****Photovoltaic materials/devices**

high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H., +, J-STQE Dec 95 1030-1036*

p-i-n diodes

AlGaAs-based p-i-n nanostruct. semicond., nonequilib. electron distrib. and high-field transport, picosecond Raman probe. *Grann, E.D., +, J-STQE Dec 95 1093-1099*

semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B., +, J-STQE Dec 95 1073-1081*

p-n junctions

GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V., +, J-STQE Jun 95 552-561*

Polarization; cf. Optical polarization**Potassium materials/devices**

KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E., +, J-STQE Apr 95 31-43*

KTiOPO₄ cryst. opt. parametric generation of Ti:sapphire laser wavelengths. *Rines, G.A., +, J-STQE Apr 95 50-57*

Power amplifiers

antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C., +, J-STQE Jun 95 129-137*

InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou, +, J-STQE Jun 95 165-172*

Power lasers

1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu, +, J-STQE Jun 95 375-381*

AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. *Shima, A., +, J-STQE Jun 95 102-109*

AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M., +, J-STQE Jun 95 728-733*

AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R., +, J-STQE Jun 95 723-727*

AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A., +, J-STQE Jun 95 734-740*

antiguidded diode laser arrays, above-threshold anal. *Nabiev, R.F., +, J-STQE Jun 95 138-149*

antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C., +, J-STQE Jun 95 129-137*

Cu vap. laser, second-harmonic and sum-freq. high av. power UV generation. *Coutts, D.W., +, J-STQE Sep 95 768-778*

Cu vap. laser, UV SHG. *Withford, M.J., +, J-STQE Sep 95 779-783*

DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J., +, J-STQE Jun 95 346-355*

GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T., +, J-STQE Jun 95 562-568*

InGaAs-GaAs 0.48- μ m circ.-grating surface-emitting DBR lasers. *Fal-lahi, M., +, J-STQE Jun 95 382-386*

InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou, +, J-STQE Jun 95 165-172*

InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M., +, J-STQE Jun 95 110-116*

InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M., +, J-STQE Jun 95 189-194*

InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim, +, J-STQE Jun 95 408-415*

InGaAsP-InP MQW monolithic laser array. *Uomi, K., +, J-STQE Jun 95 203-210*

InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U., +, J-STQE Jun 95 442-450*

InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F., +, J-STQE Jun 95 396-400*

Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M., +, J-STQE Sep 95 859-866*

semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W., +, J-STQE Jun 95 117-128*

XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y., +, J-STQE Sep 95 811-824*

ZnMgSSe blue-green LD operation. *Ishibashi, A., J-STQE Jun 95 741-748*

Process control

semicond. alloy comp. determ. during epitaxy, opt. methods. *Aspnes, D.E., J-STQE Dec 95 1054-1063*

Process monitoring

real-time opt. thermometry during semicond. proc. *Herman, I.P., J-STQE Dec 95 1047-1053*

reson.-tunneling diode growth, opt. diagnostic monitoring. *Celii, F.G., +, J-STQE Dec 95 1064-1072*

wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E., +, J-STQE Dec 95 980-986*

Pulse amplifiers; cf. Optical pulse amplifiers**Pulse compression methods; cf. Chirp modulation; Optical pulse compression****Pulsed lasers**

Cu freq.-doubled lasers for polymer high-speed UV micro-machining. *Glover, A.C.J., +, J-STQE Sep 95 830-836*

GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T., +, J-STQE Jun 95 562-568*

He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C., +, J-STQE Sep 95 805-810*

He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C., +, J-STQE Sep 95 805-810*

InGaAs-GaAs 0.48- μ m circ.-grating surface-emitting DBR lasers. *Fal-lahi, M., +, J-STQE Jun 95 382-386*

Nc-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C., +, J-STQE Sep 95 805-810*

N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H., +, J-STQE Sep 95 825-829*

SHG, unamplified high-repetition-rate, ultrashort laser pulses at Si(001) interfaces. *Dadap, J.I., +, J-STQE Dec 95 1145-1155*

Pulsed lasers; cf. Mode locked lasers**Pulse generation; cf. Optical pulse generation****Pulse shaping methods; cf. Optical pulse shaping****Pumping of lasers; cf. Laser excitation****Q****Q-switched lasers**

Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F., +, J-STQE Apr 95 58-61*

DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K., +, J-STQE Jun 95 583-591*

Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A., +, J-STQE Jun 95 569-576*

LD, self-seeded Fabry-Perot, time jitter/dyn. *Schell, M., +, J-STQE Jun 95 528-534*

semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L., +, J-STQE Jun 95 451-460*

Quantum well devices

semicond. heterostructs. and laser diodes, near-field opt. studies. *Gold-berg, B.B., +, J-STQE Dec 95 1073-1081*

Quantum well lasers

1.3 μ m semicond. lasers, gain anal. in T₀ determination. *Ackerman, D.A., +, J-STQE Jun 95 250-263*

1.3- μ m strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu, +, J-STQE Jun 95 375-381*

AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. *Shima, A., +, J-STQE Jun 95 102-109*

AlGaAs VCSEL array, spatial filtering, effect on spontaneous emission spectrum. *van Exter, M.P., +, J-STQE Jun 95 601-605*

AlGaInP VCSEL, threshold current minimization. *Chow, W.W., +, J-STQE Jun 95 649-653*

AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi, +, J-STQE Jun 95 717-722*

ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S., +, J-STQE Dec 95 1100-1107*

carrier transport, nonlin. gain coeffs. *Chin-Yi Tsai, +, J-STQE Jun 95 316-330*

DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J., +, J-STQE Jun 95 346-355*

electro-opto-thermal interact., equiv. cct. model. *Bewtra, N., +, J-STQE Jun 95 331-340*

GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T., +, J-STQE Jun 95 562-568*

GaAs-AlGaAs MQW GRINSCH laser temp. sensitivity. *Dion, M., +, J-STQE Jun 95 230-233*

GaAsP-InGaAsP long wavelength strained QW lasers, orient. depend. of opt. props. *Niwa, A., +, J-STQE Jun 95 211-217*

GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D., +, J-STQE Jun 95 661-666*

GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M., +, J-STQE Jun 95 285-292*

Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on las-ing perform. *Guodong Zhang, J-STQE Jun 95 183-188*

GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A., +, J-STQE Jun 95 293-300*

GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T., +, J-STQE Jun 95 697-706*

GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J., +, J-STQE Jun 95 173-182*

+ Check author entry for coauthors

† Check author entry for subsequent corrections/comments

- GaNP quantum well laser, threshold current strain depend. *Blood, P.*, +, *J-STQE Jun 95 707-711*
- high-speed lasers, carrier transport effects, time-domain model. *Nguyen, L. V. T.*, +, *J-STQE Jun 95 494-504*
- InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang*, +, *J-STQE Jun 95 749-756*
- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M.*, +, *J-STQE Jun 95 712-716*
- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao*, +, *J-STQE Jun 95 196-202*
- InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95 110-116*
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95 616-623*
- InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95 674-680*
- InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95 234-243*
- InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95 308-315*
- InGaAs-InGaP 0.98- μ m strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M.*, +, *J-STQE Jun 95 244-249*
- InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M.*, +, *J-STQE Jun 95 189-194*
- InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim*, +, *J-STQE Jun 95 408-415*
- InGaAsP-InP MQW-DFB LD, 1.5 μ m FM response. *Jong-In Shim*, +, *J-STQE Jun 95 516-522*
- InGaAsP-InP MQW monolithic laser array. *Uomi, K.*, +, *J-STQE Jun 95 203-210*
- InGaAsP-InP thermally tunable super-struct.-grating DBR laser spectral linewidth under wavelength tuning. *Ishii, H.*, +, *J-STQE Jun 95 401-407*
- InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95 638-648*
- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95 442-450*
- InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95 396-400*
- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95 661-666*
- InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95 654-660*
- InP-based 1.3- μ m QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95 264-274*
- monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95 539-551*
- MQW DFB laser, self-pulsating 1.55- μ m, 12-64 GHz continuous freq. tuning. *Sartorius, B.*, +, *J-STQE Jun 95 535-538*
- MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D.*, +, *J-STQE Jun 95 275-284*
- pass. antiguide VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95 629-637*
- rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95 427-432*
- ring resonator lasers, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95 757-761*
- semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B.*, +, *J-STQE Dec 95 1073-1081*
- strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang*, +, *J-STQE Jun 95 218-229*
- Quantum wells**
- GaN_{0.5}P_{0.5}-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95 173-182*
- InGaAs-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95 841-847*
- n-GaAs, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95 841-847*
- n-InP, surface modif., UV laser induced etching. *Ezaki, M.*, +, *J-STQE Sep 95 841-847*

R

Radiation effects; cf. Laser radiation effects

Raman spectroscopy

- AlGaAs-based p-i-n nanostruct. semicond., nonequilib. electron distrib. and high-field transport, picosecond Raman probe. *Grann, E.D.*, +, *J-STQE Dec 95 1093-1099*
- GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C.*, +, *J-STQE Dec 95 1119-1125*

+ Check author entry for coauthors

Rare earth materials/devices; cf. Cerium materials/devices; Erbium materials/devices; Lanthanum materials/devices; Lutetium materials/devices; Thulium materials/devices; Ytterbium materials/devices

Ray optics; cf. Geometrical optics

Receivers; cf. Optical receivers

Reflection; cf. Mirrors

Reliability; cf. Laser reliability; Semiconductor device reliability

Resists

- 193-nm lithog. technol. *Rothschild, M.*, +, *J-STQE Sep 95 916-923*

Resonance; cf. Optical resonance

Resonators; cf. Laser resonators

Ridge waveguides

- AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95 102-109*

Ga(In)As(P)-GaNAsP-GaN_{0.5}P quantum well laser, strain influence on lasing perform. *Guodong Zhang*, *J-STQE Jun 95 183-188*

InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95 110-116*

InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95 396-400*

semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95 757-761*

Ring lasers

- semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95 757-761*

S

Semiconductor optical amplifiers

- large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95 1017-1029*

Semiconductor defects

- eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D.*, +, *J-STQE Dec 95 1037-1046*

Semiconductor device doping

- HBT opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95 1011-1016*

Semiconductor device doping; cf. Semiconductor device ion implantation

Semiconductor device fabrication

- real-time opt. thermometry during semicond. proc. *Herman, I.P.*, *J-STQE Dec 95 1047-1053*

reson.-tunneling diode growth, opt. diagnostic monitoring. *Celii, F.G.*, +, *J-STQE Dec 95 1064-1072*

semicond. alloy comp. determ. during epitaxy, opt. methods. *Aspnes, D.E.*, *J-STQE Dec 95 1054-1063*

Semiconductor device fabrication; cf. Integrated circuit fabrication; Semiconductor device doping; Semiconductor device measurements

Semiconductor device ion implantation

- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95 616-623*

ZnMgSSe blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95 741-748*

Semiconductor device manufacture; cf. Semiconductor device fabrication; Semiconductor device measurements

Semiconductor device measurements

- AlGaAs-based p-i-n nanostruct. semicond., nonequilib. electron distrib. and high-field transport, picosecond Raman probe. *Grann, E.D.*, +, *J-STQE Dec 95 1093-1099*

ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S.*, +, *J-STQE Dec 95 1100-1107*

double AC photorefectance spectrosc. *Ghosh, S.*, +, *J-STQE Dec 95 1108-1112*

eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D.*, +, *J-STQE Dec 95 1037-1046*

HBT opt. charactn. *Smith, P.B.*, +, *J-STQE Dec 95 1011-1016*

high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H.*, +, *J-STQE Dec 95 1030-1036*

large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C.*, +, *J-STQE Dec 95 1017-1029*

LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R.*, *J-STQE Dec 95 987-992*

optical diagnostics of semiconductors (special issue). *J-STQE Dec 95 977-1155*

real-time opt. thermometry during semicond. proc. *Herman, I.P.*, *J-STQE Dec 95 1047-1053*

semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B.*, +, *J-STQE Dec 95 1073-1081*

thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95 993-1001*

wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H.*, +, *J-STQE Dec 95 1002-1010*

† Check author entry for subsequent corrections/comments

Semiconductor device measurements; cf. Optical spectroscopy**Semiconductor device mechanical factors**

- 1.3- μm strained MQW gain-coupled DFB lasers, high-power/high-speed perform. *Hanh Lu, +, J-STQE Jun 95 375-381*
- AlGaInP VCSEL, threshold current minimization. *Chow, W.W., +, J-STQE Jun 95 649-653*
- AlGaInP vis. laser, H effect, high temp. operation. *Won-Jin Choi, +, J-STQE Jun 95 717-722*
- ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S., +, J-STQE Dec 95 1100-1107*
- GaAsP-InGaAsP long wavelength strained QW lasers, orient. depend. of opt. props. *Niwa, A., +, J-STQE Jun 95 211-217*
- GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D., +, J-STQE Jun 95 661-666*
- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M., +, J-STQE Jun 95 285-292*
- Ga(In)As(P)-GaInAsP-GaInP quantum well laser, strain influence on lasing perform. *Guodong Zhang, J-STQE Jun 95 183-188*
- GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A., +, J-STQE Jun 95 293-300*
- GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T., +, J-STQE Jun 95 697-706*
- GaInP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J., +, J-STQE Jun 95 173-182*
- GaInP quantum well laser, threshold current strain depend. *Blood, P., +, J-STQE Jun 95 707-711*
- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M., +, J-STQE Jun 95 712-716*
- InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D., +, J-STQE Jun 95 674-680*
- InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F., +, J-STQE Jun 95 234-243*
- InGaAs-InGaP 0.98- μm strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M., +, J-STQE Jun 95 244-249*
- InGaAs-InGaP quantum well laser, tensile strained InGaAsP barriers, high-power operation. *Sagawa, M., +, J-STQE Jun 95 189-194*
- InGaAsP-InP MQW monolithic laser array. *Uomi, K., +, J-STQE Jun 95 203-210*
- InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D., +, J-STQE Jun 95 661-666*
- InP-based 1.3- μm QW laser high-temp. charact. *Seki, S., +, J-STQE Jun 95 264-274*
- MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D., +, J-STQE Jun 95 275-284*
- strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang, +, J-STQE Jun 95 218-229*
- Semiconductor device modeling**
- GaAs-AlGaAs MQW GRINSCH laser temp. sensitivity. *Dion, M., +, J-STQE Jun 95 230-233*
- InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U., +, J-STQE Jun 95 442-450*
- quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N., +, J-STQE Jun 95 331-340*
- strained quantum-well lasers with spin-orbit coupling, modeling. *Chih-Sheng Chang, +, J-STQE Jun 95 218-229*
- Semiconductor device reliability**
- InGaAlP tensile-strained MQW laser, high temp. and reliable operation. *Watanabe, M., +, J-STQE Jun 95 712-716*
- InGaAsP-InP MQW monolithic laser array. *Uomi, K., +, J-STQE Jun 95 203-210*
- ZnMgSsS blue-green LD operation. *Ishibashi, A., J-STQE Jun 95 741-748*
- Semiconductor device testing**
- eval. of defect related diffusion in semiconds. by electrooptical sampling. *Biernacki, P.D., +, J-STQE Dec 95 1037-1046*
- HBT opt. charactn. *Smith, P.B., +, J-STQE Dec 95 1011-1016*
- high-perform. n-p-n AlGaAs-GaAs HBTs, comprehensive opt. charactn. *Lu, Z.H., +, J-STQE Dec 95 1030-1036*
- large-area planar-waveguide OE devices, phase/refr. index profiling. *Hall, D.C., +, J-STQE Dec 95 1017-1029*
- LEDs, III-V epitaxial layers, high-speed photolum. mapping. *Imler, W.R., J-STQE Dec 95 987-992*
- optical diagnostics of semiconductors (special issue). *J-STQE Dec 95 977-1155*
- thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T., +, J-STQE Dec 95 993-1001*
- wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E., +, J-STQE Dec 95 980-986*
- wafer-sized semicond. device structures, nondestructive, room-temp. anal. *Pollak, F.H., +, J-STQE Dec 95 1002-1010*
- Semiconductor device thermal factors**
- AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A., +, J-STQE Jun 95 102-109*

+ Check author entry for coauthors

- GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. *Eng, L.E., +, J-STQE Jun 95 624-628*
- GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M., +, J-STQE Jun 95 681-696*
- GaInAsP-InP strained-layer quantum well laser, temp. depend. reflectivity mirror. *Kasukawa, A., +, J-STQE Jun 95 293-300*
- high-power semicond. lasers, long. spatial inhomogeneities. *Fang, W.-C.W., +, J-STQE Jun 95 117-128*
- InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M., +, J-STQE Jun 95 110-116*
- InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W., +, J-STQE Jun 95 638-648*
- InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M., +, J-STQE Jun 95 654-660*
- quantum well lasers, electro-opto-thermal interact., equiv. cct. modeling. *Bewtra, N., +, J-STQE Jun 95 331-340*
- Semiconductor diodes; cf. Light-emitting diodes; p-i-n diodes; Tunnel diodes**
- Semiconductor films**
- CdTe-doped PTFE thin films, laser deposition. *Inoue, S., +, J-STQE Sep 95 908-915*
- Semiconductor growth**
- AlGaAs ridge waveguide LD, 0.78- and 0.98- μm , chloride-assisted MOCVD. *Shima, A., +, J-STQE Jun 95 102-109*
- GaInAs-AlInAs MQW strained laser electroluminescent spectra. *Irikawa, M., +, J-STQE Jun 95 285-292*
- InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Falahi, M., +, J-STQE Jun 95 382-386*
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A., +, J-STQE Apr 95 82-91*
- Semiconductor growth; cf. Epitaxial growth**
- Semiconductor heterojunctions**
- GaInP-AlGaInP quantum well vis. laser, band struct. determ. *Meney, A.T., +, J-STQE Jun 95 697-706*
- InGaAsP/InP heterostructs., inhomog. exciton broadening and mean free path. *Jaeger, A., +, J-STQE Dec 95 1113-1118*
- semicond. heterostructs. and laser diodes, near-field opt. studies. *Goldberg, B.B., +, J-STQE Dec 95 1073-1081*
- Semiconductor-insulator interfaces**
- SHG, unamplified high-repetition-rate, ultrashort laser pulses at Si(001) interfaces. *Dadap, J.I., +, J-STQE Dec 95 1145-1155*
- Semiconductor-insulator-semiconductor devices; cf. p-i-n diodes**
- Semiconductor junctions; cf. p-n junctions; Semiconductor heterojunctions**
- Semiconductor laser arrays**
- AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P., +, J-STQE Jun 95 601-605*
- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A., +, J-STQE Jun 95 734-740*
- antiguidded diode laser arrays, above-threshold anal. *Nabiev, R.F., +, J-STQE Jun 95 138-149*
- feedback stabilization, complex coupling coeffs. *Hill, D.E., +, J-STQE Jun 95 150-164*
- GaAs-AlAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wave-length. *Eng, L.E., +, J-STQE Jun 95 624-628*
- GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M., +, J-STQE Jun 95 681-696*
- InGaAs-GaAs-AlGaAs quantum well lasers and laser arrays, threshold current. *Hanmin Zhao, +, J-STQE Jun 95 196-202*
- InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E., +, J-STQE Jun 95 616-623*
- InGaAsP-InP MQW monolithic laser array. *Uomi, K., +, J-STQE Jun 95 203-210*
- Semiconductor lasers**
- 1.3 μm semicond. lasers, gain anal. in T₀ determination. *Ackerman, D.A., +, J-STQE Jun 95 250-263*
- AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T., +, J-STQE Jun 95 606-615*
- AlGaAs narrow-stripe lasers, self-sustained pulsation. *Yuri, M., +, J-STQE Jun 95 473-479*
- AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A., +, J-STQE Jun 95 577-582*
- AlGaInP fund.-transverse-mode high-power LD, window-on-facet struct. *Watanabe, M., +, J-STQE Jun 95 728-733*
- AlGaInP index-guided high power vis. laser, HCL-assisted MOVPE. *Kobayashi, R., +, J-STQE Jun 95 723-727*
- AlGaInP vis. LD and arrays, fab., high-power charact. *Shima, A., +, J-STQE Jun 95 734-740*
- DBR short-cavity laser, electrooptic tuning, wide-band AM. *Tessler, N., +, J-STQE Jun 95 490-493*
- DFB/DBR lasers with second-order gratings, above-threshold anal. *Liew, S.K.C., J-STQE Jun 95 363-370*

† Check author entry for subsequent corrections/comments

- DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95 356-362*
- DFB laser, current-induced gain gratings. *Kazmierski, C.*, +, *J-STQE Jun 95 371-374*
- DFB lasers, complex-coupled $\lambda/4$ -shifted, flat FM response. *Okai, M.*, +, *J-STQE Jun 95 461-465*
- DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95 592-600*
- DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95 583-591*
- direct push-pull modulated enhanced-reson. freq. DFB laser in receiver expt. *Nowell, M.C.*, +, *J-STQE Jun 95 433-441*
- external opt. feedback phenomenon. *Petermann, K.*, *J-STQE Jun 95 480-489*
- Fabry-Perot semicond. laser, gain-switched, coherence and noise props. *Griffin, R.A.*, +, *J-STQE Jun 95 569-576*
- GainP-AlGaInP vis. compressively strained multiple quantum-wire lasers, CW operation. *Yoshida, J.*, +, *J-STQE Jun 95 173-182*
- grating-terminated external cavity lasers, small-sig. intens. modulation response. *Ahmed, Z.*, +, *J-STQE Jun 95 505-515*
- high-power semicond. lasers, long. spatial inhomogeneities. *Fang, W.-C.W.*, +, *J-STQE Jun 95 117-128*
- InGaAs-GaAs 0.48- μm circ.-grating surface-emitting DBR lasers. *Fal-lahi, M.*, +, *J-STQE Jun 95 382-386*
- InGaAs-GaAs VCSEL, polariz. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95 667-673*
- InGaAs-InGaAlAs-InP DFB lasers superstructure gratings, coupling coeffs. var. *Hansmann, S.*, +, *J-STQE Jun 95 341-345*
- InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95 387-395*
- mode-locked laser, sync., external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95 523-527*
- non-Markovian gain theory. *Doyeol Ahn, J-STQE Jun 95 301-307*
- opt. feedback, Sisyphus effect. *Van Tartwijk, G.H.M.*, +, *J-STQE Jun 95 466-472*
- self-seeded Fabry-Perot LD, time jitter/switch-on dyn. *Schell, M.*, +, *J-STQE Jun 95 528-534*
- semicond. heterostructs. and laser diodes, near-field opt. studies. *Gold-berg, B.B.*, +, *J-STQE Dec 95 1073-1081*
- semiconductor lasers (special issue). *J-STQE Jun 95 100-761*
- three-electrode DFB lasers, wavelength tuning and FM mechanism. *Tohyama, M.*, +, *J-STQE Jun 95 416-426*
- wafer level testing for semicond. laser manufacture, spatially resolved photolum. *Carver, G.E.*, +, *J-STQE Dec 95 980-986*
- ZnMgSSe blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95 741-748*
- Semiconductor lasers; cf. Quantum well lasers; Semiconductor optical amplifiers; Surface-emitting lasers**
- Semiconductor materials**
- AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95 44-49*
- Semiconductor materials; cf. Semiconductor films; Semiconductor superlattices**
- Semiconductor materials measurements**
- semicond. alloy comp. determ. during epitaxy, opt. methods. *Aspnes, D.E.*, *J-STQE Dec 95 1054-1063*
- Semiconductor optical amplifiers**
- antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95 129-137*
- InGaAs-GaAs high-power tapered amp., integrated output focusing lens. *Kang-Yih Liou, +, J-STQE Jun 95 165-172*
- InGaAs-InGaAsP MQW laser, carrier-phonon interact. *Nido, M.*, +, *J-STQE Jun 95 308-315*
- semicond. laser, optoelectronic microwave-range freq. mixing. *Portnoi, E.L.*, +, *J-STQE Jun 95 451-460*
- Semiconductor plasmas**
- lasers, non-Markovian gain theory. *Doyeol Ahn, J-STQE Jun 95 301-307*
- rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95 427-432*
- Semiconductor superlattices**
- GaAs-AlGaAs superlattices for intersubband infrared detect., photolum. Raman, and infrared diagnosis. *Feng, Z.C.*, +, *J-STQE Dec 95 1119-1125*
- InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang, +, J-STQE Jun 95 749-756*
- InGaAs-InGaP 0.98- μm strained quantum-well lasers, superlattice opt. confine. layer. *Usami, M.*, +, *J-STQE Jun 95 244-249*
- Sensitivity**
- GaAs-AlGaAs MQW GRINSCH laser temp. sensitivity. *Dion, M.*, +, *J-STQE Jun 95 230-233*
- InP-based 1.3- μm QW laser high-temp. charact. *Seki, S.*, +, *J-STQE Jun 95 264-274*
- MQW strained/unstrained laser max. operating temp. theory. *Evans, J.D.*, +, *J-STQE Jun 95 275-284*
- Silicon materials/devices**
- light-emitting porous Si materials sci., props., and device appls. *Faucher, P.M.*, +, *J-STQE Dec 95 1126-1139*
- spectrosc. study of red light emission in porous Si. *Prokes, S.M.*, *J-STQE Dec 95 1140-1144*
- Silver materials/devices**
- AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95 44-49*
- Sodium materials/devices**
- ZBLAN:Nd fiber laser in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95 784-791*
- Solid lasers**
- Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95 792-804*
- Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95 58-61*
- Cr⁴⁺-doped laser host lattices, tunable output. *Pollock, C.R.*, +, *J-STQE Apr 95 62-66*
- LiF:F₂ color center laser progress. *Mirov, S.B.*, +, *J-STQE Apr 95 22-30*
- rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95 82-91*
- Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95 50-57*
- Tm:YAlO₃ 1.94- μm laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95 78-81*
- tunable solid-state lasers (special issue). *J-STQE Apr 95 1-91*
- Yb:Sr₅(PO₄)₃F 1.047- μm energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95 67-77*
- Solid lasers; cf. Optical fiber lasers; Semiconductor lasers**
- Solid state plasmas; cf. Semiconductor plasmas**
- Solitons; cf. Optical solitons**
- Space charge**
- GaAs-GaAlAs waveguide saturable absorbers, carrier heating/sweepout dyn. *Uskov, A.V.*, +, *J-STQE Jun 95 552-561*
- Sparks**
- Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95 945-948*
- Spatial filters**
- AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95 601-605*
- Special issues/sections**
- optical diagnostics of semiconductors (special issue). *J-STQE Dec 95 977-1155*
- semiconductor lasers (special issue). *J-STQE Jun 95 100-761*
- short wavelength lasers and applications (special issue). *J-STQE Sep 95 765-975*
- tunable solid-state lasers (special issue). *J-STQE Apr 95 1-91*
- Spectroscopy**
- KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95 31-43*
- Spectroscopy; cf. Electron spectroscopy; Fourier spectroscopy; Infrared spectroscopy; Mass spectroscopy; Optical spectroscopy**
- Spontaneous emission**
- AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95 606-615*
- AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95 601-605*
- Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95 945-948*
- Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95 924-930*
- ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S.*, +, *J-STQE Dec 95 1100-1107*
- corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95 1156*
- Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95 949-957*
- semicond. laser, high-power, long. spatial inhomogeneities. *Fang, W.-C.W.*, +, *J-STQE Jun 95 117-128*
- Stability; cf. Laser stability**
- Stimulated emission**
- InAs-InAs_xSb_{1-x} type-II superlattice midwave IR lasers. *Yong-Hang Zhang, +, J-STQE Jun 95 749-756*
- InGaAs-InGaAsP-InGaP LD temp. depend. efficiency and modulation charact. *Nabiev, R.F.*, +, *J-STQE Jun 95 234-243*
- Tm:YAlO₃ 1.94- μm laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95 78-81*
- Yb:Sr₅(PO₄)₃F 1.047- μm energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95 67-77*

Stimulated emission; cf. Lasers**Strain**

ASE spectrosc. in strained quantum-well lasers. *Chang, C.-S.*, +, *J-STQE Dec 95* 1100-1107

Superlattices; cf. Semiconductor superlattices**Surface discharges; cf. Corona****Surface-emitting lasers**

AlGaAs DBR VCSEL, microcavity vac.-field config., spontaneous emission power. *Zhang, T.*, +, *J-STQE Jun 95* 606-615

AlGaAs VCSEL array, spatial filtering effect on spontaneous emission spectrum. *van Exter, M.P.*, +, *J-STQE Jun 95* 601-605

AlGaInP VCSEL, threshold current minimization. *Chow, W.W.*, +, *J-STQE Jun 95* 649-653

GaAs-ALAs Fabry-Perot vert. cavity arrays, spatially chirped reson. wavelength. *Eng, L.E.*, +, *J-STQE Jun 95* 624-628

GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95* 681-696

GaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666

InGaAs-GaAs MQW VCSEL and 2D arrays, fab. and fiber coupling. *Zeeb, E.*, +, *J-STQE Jun 95* 616-623

InGaAs-GaAs quantum well VCSEL, anisotropic gain distrib., polaris. control. *Sun, D.*, +, *J-STQE Jun 95* 674-680

InGaAs-GaAs VCSEL, polaris. control, birefr. metal/dielec. polarizer. *Mukaihara, T.*, +, *J-STQE Jun 95* 667-673

InGaAs quantum well VCSEL design for single-mode operation. *Scott, J.W.*, +, *J-STQE Jun 95* 638-648

InGaAs QW external cavity laser act. mode-locking/data transm. *Fiedler, U.*, +, *J-STQE Jun 95* 442-450

InGaAs VCSEL, gain depend. polaris. props. *Choquette, K.D.*, +, *J-STQE Jun 95* 661-666

InGaAs VCSEL with broad-gain bandwidth, temp. charact. *Kajita, M.*, +, *J-STQE Jun 95* 654-660

pass. antiguide VCSEL, single-mode operation. *Wu, Y.A.*, +, *J-STQE Jun 95* 629-637

Synchronization

semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527

T**Technological innovation**

EUV lithog. at 13 nm, current status. *Stulen, R.H.*, *J-STQE Sep 95* 970-975

Technology forecasting

EUV lithog. at 13 nm, current status. *Stulen, R.H.*, *J-STQE Sep 95* 970-975

Temperature measurement

real-time opt. thermometry during semicond. proc. *Herman, I.P.*, *J-STQE Dec 95* 1047-1053

Testing; cf. Manufacturing testing; Semiconductor device testing**Thermal factors; cf. Ablation; Laser thermal factors; Semiconductor device thermal factors****Thermal variables measurement; cf. Temperature measurement****Thin film transistors**

thin-film transistor arrays testing/charactn., opt. charge-sensing method. *Kido, T.*, +, *J-STQE Dec 95* 993-1001

Thulium materials/devices

Tm:YAlO₃ 1.94- μ m laser, biomedical appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81

Time domain analysis

monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551

quantum well high-speed lasers, carrier transport effects, time-domain model. *Nguyen, L.V.T.*, +, *J-STQE Jun 95* 494-504

Timing jitter

LD, self-seeded Fabry-Perot, time jitter/dyn. *Schell, M.*, +, *J-STQE Jun 95* 528-534

Titanium materials/devices

Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57

Transistors; cf. Thin film transistors**Transition metal materials/devices; cf. Chromium materials/devices; Copper materials/devices; Gold materials/devices; Silver materials/devices; Titanium materials/devices; Yttrium materials/devices; Zirconium materials/devices****Traveling wave amplifiers; cf. Semiconductor optical amplifiers****Tunable circuits/devices**

Ti:sapphire laser wavelengths, nonlin. conversion. *Rines, G.A.*, +, *J-STQE Apr 95* 50-57

Tunable circuits/devices; cf. Laser tuning; Tunable oscillators**Tunable lasers; cf. Laser tuning****Tunable oscillators**

AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49

KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95* 31-43

Tuning

AgGaSe₂ noncritically phase matched mid-IR generation by opt. parametric oscillator. *Komine, H.*, +, *J-STQE Apr 95* 44-49

KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95* 31-43

Tunnel diodes

reson.-tunneling diode growth, opt. diagnostic monitoring. *Celii, F.G.*, +, *J-STQE Dec 95* 1064-1072

U**Ultrafast optics**

AlGaAs-based p-i-n nanostruct. semicond., nonequib. electron distrib. and high-field transport, picosecond Raman probe. *Grann, E.D.*, +, *J-STQE Dec 95* 1093-1099

AlGaAs single-strip mode-locked LD, nonlin. chirp compensation. *Azouz, A.*, +, *J-STQE Jun 95* 577-582

Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804

DFB semicond. laser, femtosecond pulse generation, soliton effect compression. *Ahmed, K.A.*, +, *J-STQE Jun 95* 592-600

DFB semicond. laser with absorptive grating, gain-switching operation. *Sudoh, T.K.*, +, *J-STQE Jun 95* 583-591

InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400

KTiOPO₄ broadly tunable fs opt. parametric oscillators. *Spence, D.E.*, +, *J-STQE Apr 95* 31-43

monolithic multiple colliding pulse mode-locked QW laser. *Martins-Filho, J.F.*, +, *J-STQE Jun 95* 539-551

N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829

polymers, high-speed UV micro-machining, freq.-doubled Cu vap. lasers. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836

quantum well high-speed lasers, carrier transport effects, time-domain model. *Nguyen, L.V.T.*, +, *J-STQE Jun 95* 494-504

semicond. quantum well laser, carrier transport, nonlin. gain coeffs. *Chin-Yi Tsai, +*, *J-STQE Jun 95* 316-330

SHG, unamplified high-repetition-rate, ultrashort laser pulses at Si(001) interfaces. *Dadap, J.I.*, +, *J-STQE Dec 95* 1145-1155

Xe, VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899

Ultraviolet generation

Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930

Ar²⁺F⁺ ionic excimers, VUV spectra. *Chi Zhou, +*, *J-STQE Sep 95* 872-876

Ce³⁺ activated materials, tunable UV ultrafast lasing, 10 ns pumping. *Sarukura, N.*, +, *J-STQE Sep 95* 792-804

Cr:LiSrAlF₆ Q-switched laser freq. tripling, UV region. *Pinto, J.F.*, +, *J-STQE Apr 95* 58-61

Cu freq.-doubled lasers for polymer high-speed UV micro-machining. *Glover, A.C.J.*, +, *J-STQE Sep 95* 830-836

Cu vap. laser, second-harmonic and sum-freq. high av. power UV generation. *Coutts, D.W.*, +, *J-STQE Sep 95* 768-778

Cu vap. laser, UV SHG. *Withford, M.J.*, +, *J-STQE Sep 95* 779-783

(HeAr)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885

He-Au⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810

He-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810

Hg vap., intense VUV coherent light generation, nonlin. effects. *Museur, L.*, +, *J-STQE Sep 95* 900-907

(KrCs)⁺ ionic excimer, electron-beam excitation, VUV emission. *Tischler, H.*, +, *J-STQE Sep 95* 877-885

Kr²⁺F⁺ ionic excimers, VUV spectra. *Chi Zhou, +*, *J-STQE Sep 95* 872-876

Nd:YAG, solid-state CW freq.-quadrupled laser. *Oka, M.*, +, *J-STQE Sep 95* 859-866

Nd:ZBLAN fiber lasers in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791

Ne-Cu⁺ high-gain hollow-cathode lasers for UV and VUV. *Tobin, R.C.*, +, *J-STQE Sep 95* 805-810

Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
 N₂ laser, ultra-fast mag. pulse compression cct. *Seki, H.*, +, *J-STQE Sep 95* 825-829
 short wavelength lasers and applications (special issue). *J-STQE Sep 95* 765-975
 SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
 XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
 Xe excimer lamp excitation by quasi-CW jet discharges. *Kawanaka, J.*, +, *J-STQE Sep 95* 852-858
 Xe²⁺ Auger laser, pumping by laser-prod. target materials. *Dennis, T.*, +, *J-STQE Sep 95* 867-871
 Xe, VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899

V

Vapor deposition

CdTe-doped PTFE thin films, laser deposition. *Inoue, S.*, +, *J-STQE Sep 95* 908-915

Vapor deposition; cf. CVD

W

Waveguide lasers

AlGaAs ridge waveguide LD, 0.78- and 0.98- μ m, chloride-assisted MOCVD. *Shima, A.*, +, *J-STQE Jun 95* 102-109
 antiguided diode laser arrays, above-threshold anal. *Nabiev, R.F.*, +, *J-STQE Jun 95* 138-149
 antiresonant-reflective-opt. waveguide laser for MOPA. *Zmudzinski, C.*, +, *J-STQE Jun 95* 129-137
 DFB laser, bent waveguides and chirped gratings. *Hillmer, H.*, +, *J-STQE Jun 95* 356-362
 DFB laser with S-bent waveguide, high-power single-mode operation. *Salzman, J.*, +, *J-STQE Jun 95* 346-355
 GaAlAs LD, 800 mW peak-power self-sustained pulsation. *Takayama, T.*, +, *J-STQE Jun 95* 562-568
 GaAs-AlGaAs etched-well VCSEL arrays, thermal anal. *Osinski, M.*, +, *J-STQE Jun 95* 681-696
 Ga(In)As(P)-GaInAsP-GaN quantum well laser, strain influence on lasing perform. *Guodong Zhang, J-STQE Jun 95* 183-188
 InGaAs-GaAs-InGaP high-power lasers with Ga₂O₃ facet coatings, IR microscopy. *Passlack, M.*, +, *J-STQE Jun 95* 110-116
 InGaAsP-InGaAsP MQW waveguide laser current injection, refr. index/loss changes. *Jong-In Shim, +, J-STQE Jun 95* 408-415
 InGaAsP-InP distributed forward coupled waveguide laser. *Amann, M.-C.*, +, *J-STQE Jun 95* 387-395
 InGaAs subns tunable DBR lasers, integrated InGaAsP electrooptical Bragg sect. *Delorme, F.*, +, *J-STQE Jun 95* 396-400
 rare earth doped fluoride planar waveguide laser oscillator, MBE fab. *McFarlane, R.A.*, +, *J-STQE Apr 95* 82-91
 semicond. laser, mode-locked, synchronization with external pulse stream. *Khalfin, V.B.*, +, *J-STQE Jun 95* 523-527
 semicond. ring resonator laser, self-aligned fab. proc. *Krauss, T.F.*, +, *J-STQE Jun 95* 757-761
 SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944

Waveguides; cf. Optical waveguides; Ridge waveguides

Wavelength division multiplexing

rapidly-tunable QW DFB laser, carrier-transport effects. *Morinaga, M.*, +, *J-STQE Jun 95* 427-432

WDM; cf. Wavelength division multiplexing

X

Xenon materials/devices

excimer lamps excitation by quasi-CW jet discharges. *Kawanaka, J.*, +, *J-STQE Sep 95* 852-858
 Ne-Xe-Cs gas mixtures, discharge excitation, excimer VUV emission study. *Tischler, H.*, +, *J-STQE Sep 95* 886-890
 VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899
 XeCl excimer 2-kW laser, surface corona preionization scheme, spiker-sustainer cct. *Sato, Y.*, +, *J-STQE Sep 95* 811-824
 Xe²⁺ Auger laser, pumping by laser-prod. target materials. *Dennis, T.*, +, *J-STQE Sep 95* 867-871

X-ray lasers

Ar discharge-driven 46.9-nm amp., gain-length approaching saturation. *Rocca, J.J.*, +, *J-STQE Sep 95* 945-948
 Ar₂ excimer lasers, electron beam pumped, unstable resonator, VUV spectral region. *Katto, M.*, +, *J-STQE Sep 95* 924-930
 corrections to "A computational investigation of the neon-like germanium collisionally-pumped laser considering the effect of prepulses" (Sept 95 949-957). *Healy, S.B.*, +, *J-STQE Dec 95* 1156
 Ga, Ne-like lasing, prepulse effect. *Fill, E.E.*, +, *J-STQE Sep 95* 958-961
 Ge, Ne-like collisionally-pumped laser, prepulses effect, computer model. *Healy, S.B.*, +, *J-STQE Sep 95* 949-957
 Li⁺ opt. field-induced ionization X-ray laser, preformed plasma. *Midorikawa, K.*, +, *J-STQE Sep 95* 931-940
 short wavelength lasers and applications (special issue). *J-STQE Sep 95* 765-975
 SW capillary lasers, tunable spatial coherence. *Kukhlevsky, S.V.*, +, *J-STQE Sep 95* 941-944
 Ta laser double-pass, CrB₂-C multilayer mirror damage, computer simul. *Balakireva, L.L.*, +, *J-STQE Sep 95* 962-969
 Xe, VUV subpicosecond pulse compression, induced-PM. *Yamada, T.*, +, *J-STQE Sep 95* 891-899

X-ray lithography

EUV lithog. at 13 nm, current status. *Stulen, R.H.*, *J-STQE Sep 95* 970-975

Y

YAG lasers; cf. Neodymium:YAG lasers

Ytterbium materials/devices

Yb:Sr₅(PO₄)₃F 1.047- μ m energy storage opt. amp. *Marshall, C.D.*, +, *J-STQE Apr 95* 67-77
 Yb³⁺:SiO₂ fiber lasers, sources 1, 1.2 μ m. *Pask, H.M.*, +, *J-STQE Apr 95* 2-13

Yttrium materials/devices

YAlO₃:Tm laser, med. appls. *Stoneman, R.C.*, +, *J-STQE Apr 95* 78-81

Z

Zinc materials/devices

laser-prod. plasma target materials for Xe²⁺ Auger laser pumping. *Dennis, T.*, +, *J-STQE Sep 95* 867-871

ZnMgSSe blue-green LD operation. *Ishibashi, A.*, *J-STQE Jun 95* 741-748

Zirconium materials/devices

ZBLAN:Nd fiber laser in UV and vis., upconversion pumping. *Funk, D.S.*, +, *J-STQE Sep 95* 784-791